

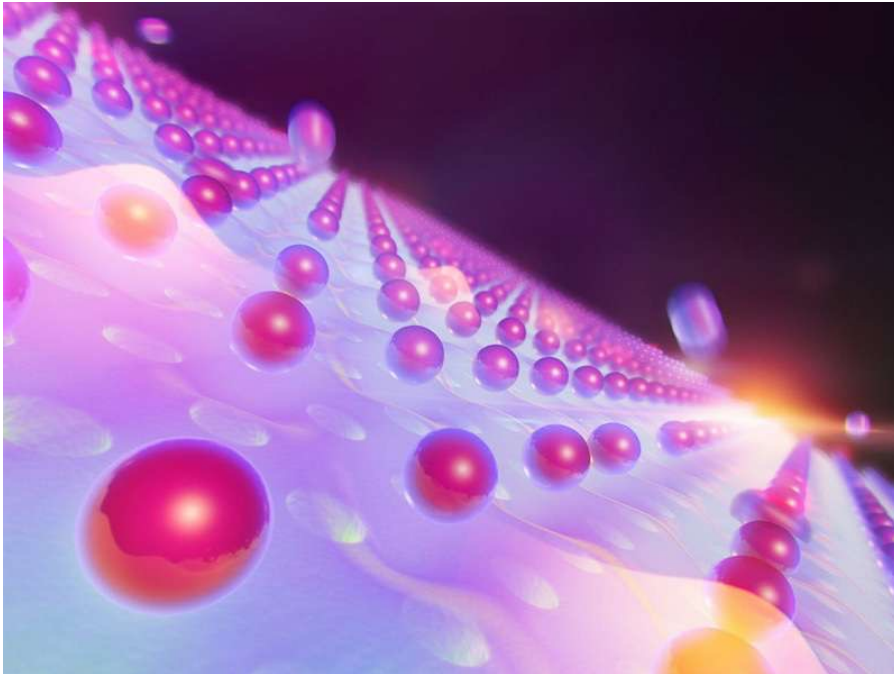
Computational Materials Physics

Density Functional Theory

Physics Concerto

2023 November 8th

$$\left(-\sum_i \frac{\nabla_i^2}{2} - \sum_I \frac{\nabla_I^2}{2M_I} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|} + \frac{1}{2} \sum_{I \neq J} \frac{Z_I Z_J}{|\mathbf{R}_I - \mathbf{R}_J|} \right) \Psi = E_{\text{tot}} \Psi.$$





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10 more professors in
Chemistry, ECE, ME, Materials E, ...

Computational Materials Physics

$$\left(-\sum_i \frac{\nabla_i^2}{2} - \sum_I \frac{\nabla_I^2}{2M_I} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|} + \frac{1}{2} \sum_{I \neq J} \frac{Z_I Z_J}{|\mathbf{R}_I - \mathbf{R}_J|} \right) \Psi = E_{\text{tot}} \Psi.$$



Thousands of Physicists
Billions of dollars
Bad for environment

What would you do first?

Some chemists
\$5
Eco-friendly

Density Functional Theory

Generalized gradient approximation made simple

Authors

John P Perdew, Kieron Burke, Matthias Ernzerhof

Publication date

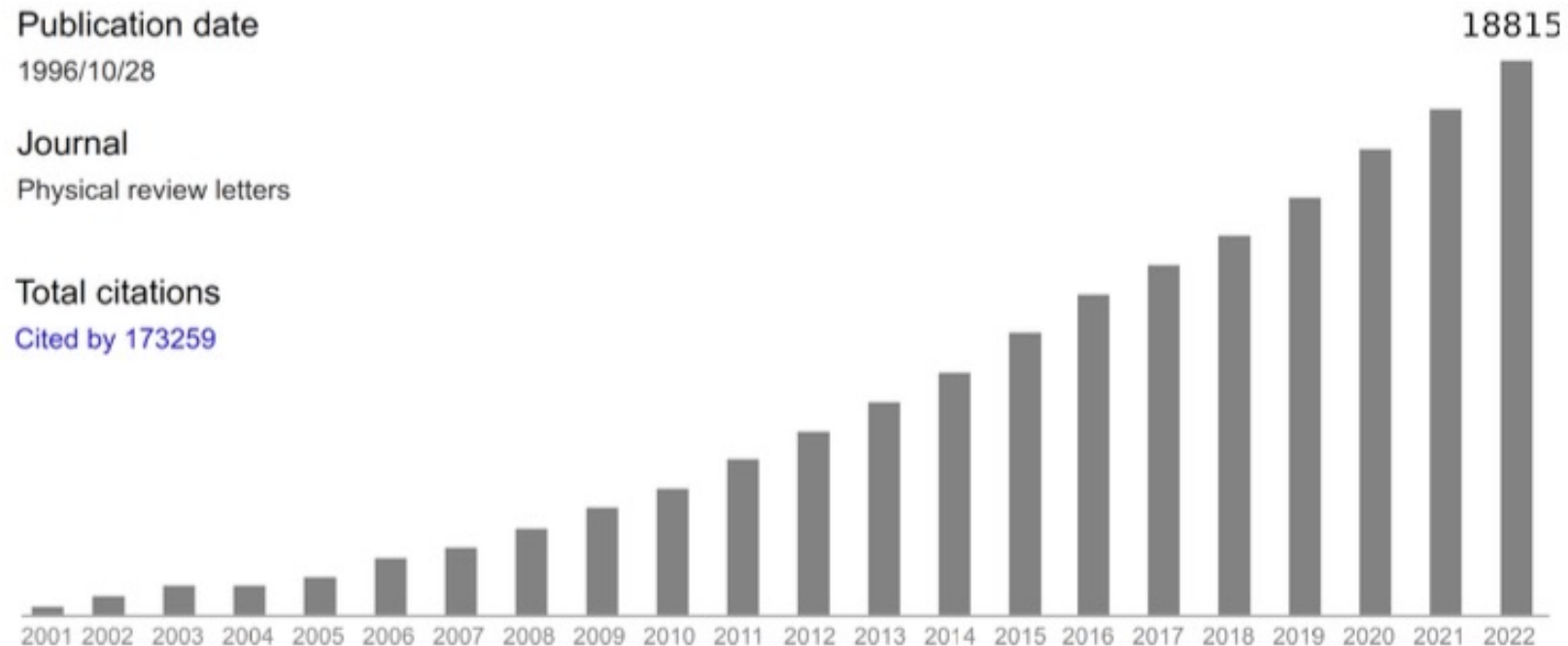
1996/10/28

Journal

Physical review letters

Total citations

Cited by 173259



Density Functional Theory

- 1964** Hohenberg–Kohn theorem and Kohn–Sham formulation
- 1972** Relativistic extension of density functional theory
- 1980** Local density approximation for exchange and correlation
- 1984** Time-dependent density functional theory
- 1985** First-principles molecular dynamics
- 1986** Quasiparticle corrections for insulators
- 1987** Density functional perturbation theory
- 1988** Towards quantum chemistry accuracy
- 1991** Hubbard-corrected density functional theory
- 1996** The generalized gradient approximation

Density Functional Theory

You've never heard spin today... but works perfectly for a magnetic system as well.

$$\left(-\sum_i \frac{\nabla_i^2}{2} - \sum_I \frac{\nabla_I^2}{2M_I} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|} + \frac{1}{2} \sum_{I \neq J} \frac{Z_I Z_J}{|\mathbf{R}_I - \mathbf{R}_J|} \right) \Psi = E_{\text{tot}} \Psi.$$

Clamped nuclei

$$\left(\underbrace{-\sum_i \frac{\nabla_i^2}{2}}_{\text{single-electron}} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \underbrace{\frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|}}_{\text{many-electron}} \right) \Psi = E \Psi. \quad E = E_{\text{tot}} - \frac{1}{2} \sum_{I \neq J} \frac{Z_I Z_J}{|\mathbf{R}_I - \mathbf{R}_J|}.$$

$$\hat{H}(\mathbf{r}_1, \dots, \mathbf{r}_N) = \sum_i \hat{H}_0(\mathbf{r}_i) + \frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|}$$

$$n(\mathbf{r}) = \sum_i |\phi_i(\mathbf{r})|^2$$

$$\Psi(\mathbf{r}_1, \mathbf{r}_2, \dots, \mathbf{r}_N) = \phi_1(\mathbf{r}_1) \cdots \phi_N(\mathbf{r}_N) \quad \Psi(\mathbf{r}_1, \mathbf{r}_2) = \frac{1}{\sqrt{2}} \begin{vmatrix} \phi_1(\mathbf{r}_1) & \phi_1(\mathbf{r}_2) \\ \phi_2(\mathbf{r}_1) & \phi_2(\mathbf{r}_2) \end{vmatrix}$$

Independent electron approximation

Slater determinant

Density Functional Theory

$$\left(\underbrace{-\sum_i \frac{\nabla_i^2}{2}}_{\text{single-electron}} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \underbrace{\frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|}}_{\text{many-electron}} \right) \Psi = E \Psi. \quad \Psi(\mathbf{r}_1, \mathbf{r}_2, \dots, \mathbf{r}_N) = \phi_1(\mathbf{r}_1) \cdots \phi_N(\mathbf{r}_N)$$

$$\left[-\frac{\nabla^2}{2} + V_n(\mathbf{r}) + V_H(\mathbf{r}) \right] \phi_i(\mathbf{r}) = \varepsilon_i \phi_i(\mathbf{r}) \quad \text{Hartree or mean-field approximation}$$

$$n(\mathbf{r}) = \sum_i |\phi_i(\mathbf{r})|^2,$$

$$\nabla^2 V_H(\mathbf{r}) = -4\pi n(\mathbf{r}).$$

Self-consistent field method

$\Sigma \approx \text{wavy line} \circlearrowleft + \text{wavy line} \circlearrowright, \quad \text{with } \parallel = | + \Sigma,$

Density Functional Theory

$$\left(\underbrace{-\sum_i \frac{\nabla_i^2}{2}}_{\text{single-electron}} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \underbrace{\frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|}}_{\text{many-electron}} \right) \Psi = E \Psi. \quad \Psi(\mathbf{r}_1, \mathbf{r}_2, \dots, \mathbf{r}_N) = \phi_1(\mathbf{r}_1) \cdots \phi_N(\mathbf{r}_N)$$

$$\left[-\frac{\nabla^2}{2} + V_n(\mathbf{r}) + V_H(\mathbf{r}) \right] \phi_i(\mathbf{r}) + \underbrace{\int d\mathbf{r}' V_X(\mathbf{r}, \mathbf{r}') \phi_i(\mathbf{r}')}_{\text{Including exchange interaction}} = \varepsilon_i \phi_i(\mathbf{r}),$$

$$n(\mathbf{r}) = \sum_i |\phi_i(\mathbf{r})|^2,$$

Including exchange interaction

$$\nabla^2 V_H(\mathbf{r}) = -4\pi n(\mathbf{r}).$$

$$V_H(\mathbf{r}) = \sum_j \int d\mathbf{r}' \frac{|\phi_j(\mathbf{r}')|^2}{|\mathbf{r} - \mathbf{r}'|},$$

Self-interaction for localized orbitals

$$V_X(\mathbf{r}, \mathbf{r}') = - \sum_j \frac{\phi_j^*(\mathbf{r}') \phi_j(\mathbf{r})}{|\mathbf{r} - \mathbf{r}'|}.$$

Nonlocal

Density Functional Theory

Walter Kohn



Kohn in 2012

Nobel prize in Chemistry 1998

Schwinger's student

E is the energy of the ground state: $n(\mathbf{r}) \xrightarrow{F} E \quad E = F[n(\mathbf{r})]$

E is the energy of an excited state: $\Psi(\mathbf{r}_1, \dots, \mathbf{r}_N) \xrightarrow{\mathcal{F}} E \quad E = \mathcal{F}[\Psi(\mathbf{r}_1, \dots, \mathbf{r}_N)]$

Hohenberg-Kohn theorem

$$\left. \frac{\delta F[n]}{\delta n} \right|_{n_0} = 0.$$

$$E = \langle \Psi | \hat{H} | \Psi \rangle = \int d\mathbf{r}_1 \dots d\mathbf{r}_N \Psi^*(\mathbf{r}_1, \dots, \mathbf{r}_N) \hat{H} \Psi(\mathbf{r}_1, \dots, \mathbf{r}_N). \quad (3.1)$$

$$\hat{H}(\mathbf{r}_1, \mathbf{r}_2, \dots, \mathbf{r}_N) = - \sum_i \frac{1}{2} \nabla_i^2 + \sum_i V_n(\mathbf{r}_i) + \frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|}. \quad (3.2)$$

- 1) In the ground state the electron density determines uniquely the external potential V_n in eqn 3.2:
 $n \rightarrow V_n$.
- 2) In any quantum state the external potential, V_n , determines uniquely the many-electron wavefunction:
 $V_n \rightarrow \Psi$.
- 3) In any quantum state the total energy, E , is a functional of the many-body wavefunction through eqn 3.1:
 $\Psi \rightarrow E$.

The ground state energy of a many-electron system is expressed as a functional of the electron density!

Density Functional Theory!

Density Functional Theory

E is the energy of the ground state:

$$n(\mathbf{r}) \xrightarrow{F} E \quad E = F[n(\mathbf{r})]$$

Hohenberg-Kohn theorem

$$\left. \frac{\delta F[n]}{\delta n} \right|_{n_0} = 0.$$

$$\left(-\sum_i \frac{\nabla_i^2}{2} - \sum_I \frac{\nabla_I^2}{2M_I} - \sum_{i,I} \frac{Z_I}{|\mathbf{r}_i - \mathbf{R}_I|} + \frac{1}{2} \sum_{i \neq j} \frac{1}{|\mathbf{r}_i - \mathbf{r}_j|} + \frac{1}{2} \sum_{I \neq J} \frac{Z_I Z_J}{|\mathbf{R}_I - \mathbf{R}_J|} \right) \Psi = E_{\text{tot}} \Psi.$$

$$F[n] = \int d\mathbf{r} n(\mathbf{r}) V_n(\mathbf{r}) - \sum_i \int d\mathbf{r} \psi_i^*(\mathbf{r}) \frac{\nabla^2}{2} \psi_i(\mathbf{r}) + \frac{1}{2} \iint d\mathbf{r} d\mathbf{r}' \frac{n(\mathbf{r})n(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + E_{xc}[n].$$

$$\left[-\frac{1}{2} \nabla^2 + V_n(\mathbf{r}) + V_H(\mathbf{r}) + V_{xc}(\mathbf{r}) \right] \phi_i(\mathbf{r}) = \varepsilon_i \phi_i(\mathbf{r}).$$

Kohn-Sham equation

Nothing but just Hartree potential...

'The Kohn-Sham theory may be regarded as the formal exactification of Hartree theory. With the exact E_{xc} and V_{xc} all many-body effects are in principle included. Clearly this directs attention to the functional $E_{xc}[n]$. The practical usefulness of ground-state DFT depends entirely on whether approximations for the functional $E_{xc}[n]$ could be found, which are at the same time sufficiently simple and sufficiently accurate.'



Density Functional Theory

But how can we determine exchange-correlation potential?

Assume homogeneous electron gas first

$$E_X = -\frac{3}{4} \left(\frac{3}{\pi}\right)^{\frac{1}{3}} n^{\frac{4}{3}} V.$$

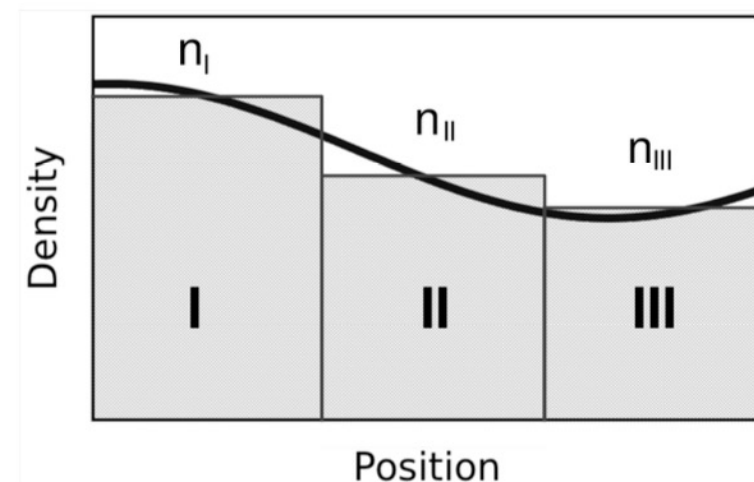
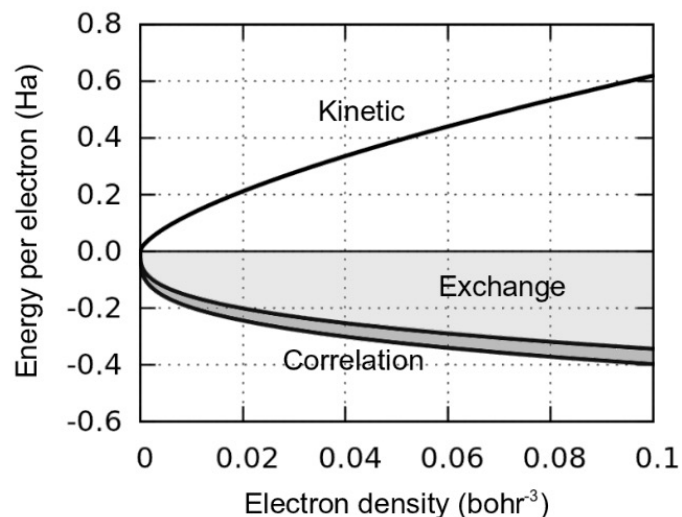
$$E_C = nV \cdot \begin{cases} 0.0311 \ln r_s - 0.0480 + 0.002 r_s \ln r_s - 0.0116 r_s & \text{if } r_s < 1, \\ \frac{-0.1423}{1 + 1.0529\sqrt{r_s} + 0.3334 r_s} & \text{if } r_s \geq 1. \end{cases}$$

From stochastic Monte Carlo

$$E_{\text{correl. (high density)}} = 0.046 + A^{(2)} \int \frac{d^3 q}{q^3} + r_s A^{(3)} \int \frac{d^3 q}{q^5} + r_s^2 A^{(4)} \int \frac{d^3 q}{q^7} + \dots$$

$$\frac{E_{\text{correl.}}}{N} = 0.0622 \ln r_s - 0.096 + \mathcal{O}(r_s),$$

First two terms are by Gell-Mann and Brueckner (1957)



Density Functional Theory

$$\left[-\frac{1}{2}\nabla^2 + V_{\text{tot}}(\mathbf{r}) \right] \phi_i(\mathbf{r}) = \epsilon_i \phi_i(\mathbf{r}),$$

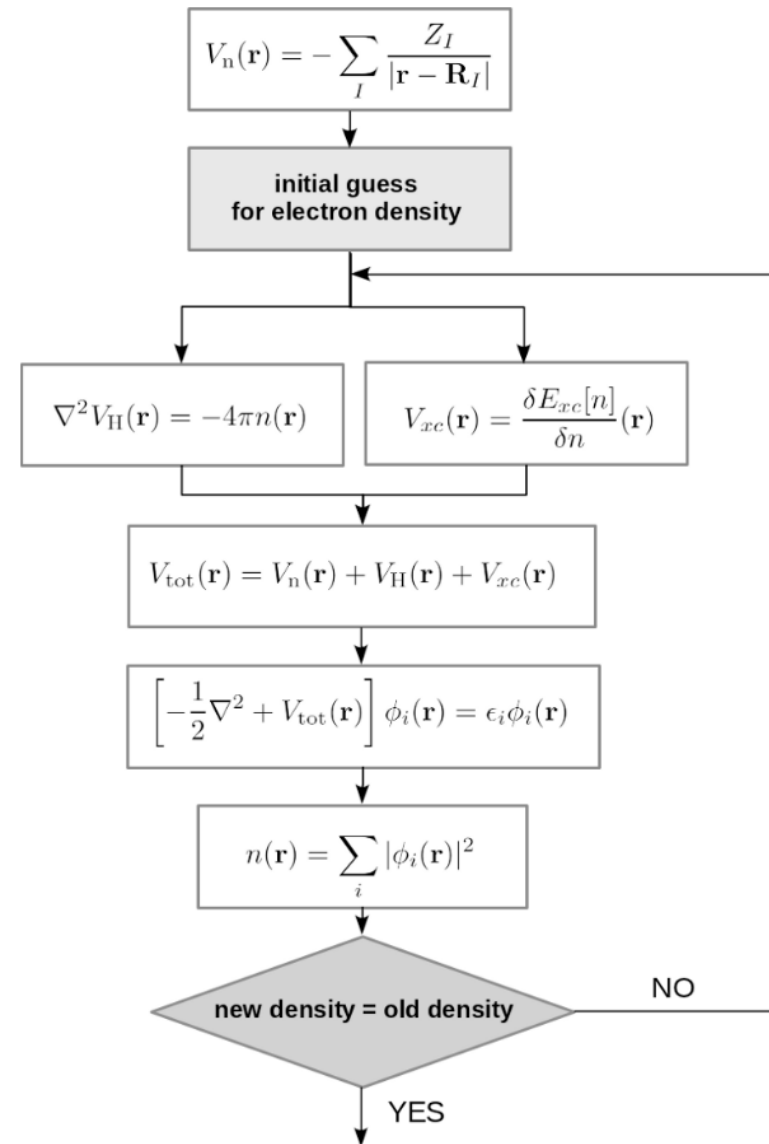
$$V_{\text{tot}}(\mathbf{r}) = V_{\text{n}}(\mathbf{r}) + V_{\text{H}}(\mathbf{r}) + V_{\text{xc}}(\mathbf{r}),$$

$$V_{\text{n}}(\mathbf{r}) = -\sum_I \frac{Z_I}{|\mathbf{r} - \mathbf{R}_I|},$$

$$\nabla^2 V_{\text{H}}(\mathbf{r}) = -4\pi n(\mathbf{r}),$$

$$V_{\text{xc}}(\mathbf{r}) = \frac{\delta E_{\text{xc}}[n]}{\delta n}(\mathbf{r}),$$

$$n(\mathbf{r}) = \sum_i |\phi_i(\mathbf{r})|^2.$$



Self-consistent calculation!

Energy, charge density

Planewaves Representation

$$\left[-\frac{1}{2}\nabla^2 + V_n(\mathbf{r}) + V_H(\mathbf{r}) + V_{xc}(\mathbf{r}) \right] \phi_i(\mathbf{r}) = \varepsilon_i \phi_i(\mathbf{r}).$$

$$6\Phi(p, q, r) - [\Phi(p+1, q, r) + \Phi(p-1, q, r) + \Phi(p, q+1, r) + \Phi(p, q-1, r) + \Phi(p, q, r+1) + \Phi(p, q, r-1)] + 2\left(\frac{a}{N_p}\right)^2 V_{\text{tot}}(p, q, r)\Phi(p, q, r) = 2\left(\frac{a}{N_p}\right)^2 \varepsilon \Phi(p, q, r).$$

$$H \begin{bmatrix} \Phi(1) \\ \Phi(2) \\ \dots \\ \Phi(N_p^3) \end{bmatrix} = \varepsilon \begin{bmatrix} \Phi(1) \\ \Phi(2) \\ \dots \\ \Phi(N_p^3) \end{bmatrix}, \quad N_p \sim 200$$

real space representation requires too many data points to solve the differential equation

$$\mathbf{G} = m_1 \mathbf{b}_1 + m_2 \mathbf{b}_2 + m_3 \mathbf{b}_3, \text{ with } m_1, m_2, m_3 \text{ integers.}$$

$$\phi(\mathbf{r}) = \sum_{\mathbf{G}} c(\mathbf{G}) \exp(i\mathbf{G} \cdot \mathbf{r}).$$

$$c(\mathbf{G}) = \frac{1}{a^3} \int d\mathbf{r} \exp(-i\mathbf{G} \cdot \mathbf{r}) \phi(\mathbf{r}).$$

$$\exp[i\mathbf{G} \cdot (\mathbf{r} + a\mathbf{u}_x)] = \exp(i\mathbf{G} \cdot \mathbf{r}) \exp(ia\mathbf{G} \cdot \mathbf{u}_x) = \exp(i\mathbf{G} \cdot \mathbf{r}) \exp(i2\pi m_1) = \exp(i\mathbf{G} \cdot \mathbf{r}),$$

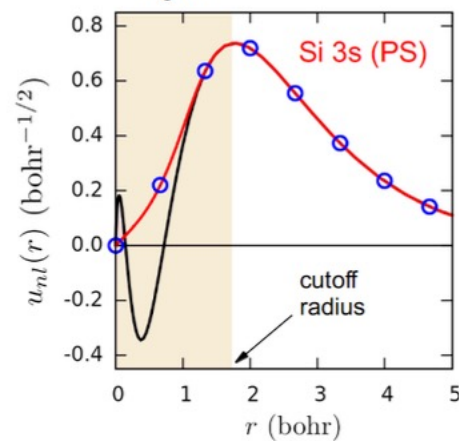
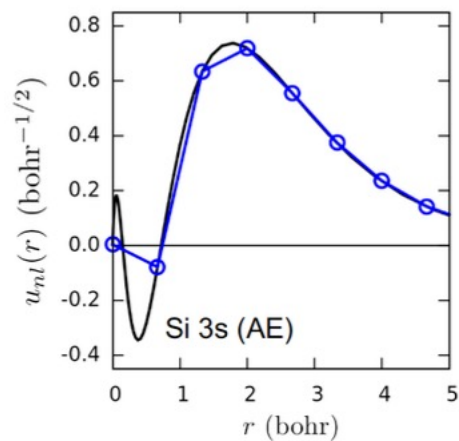
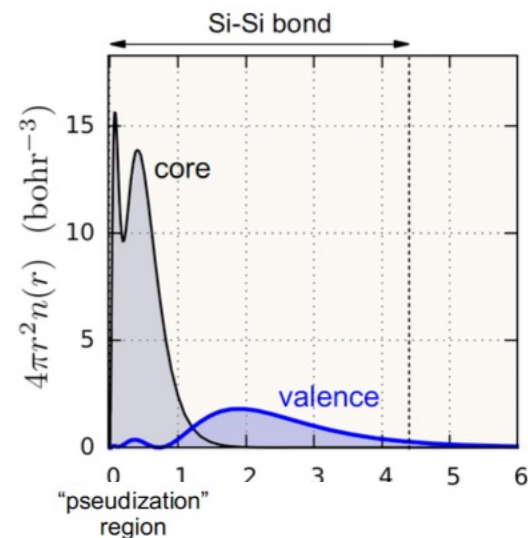
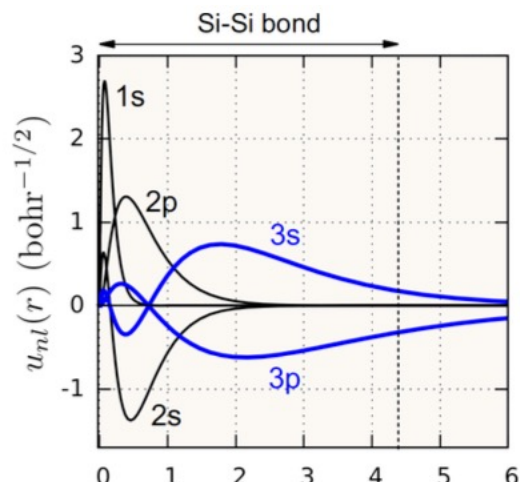
Periodicity is implemented automatically

$$\frac{|\mathbf{G}|^2}{2} c(\mathbf{G}) + \sum_{\mathbf{G}'} v_{\text{tot}}(\mathbf{G} - \mathbf{G}') c(\mathbf{G}') = \varepsilon c(\mathbf{G}),$$

Expensive part

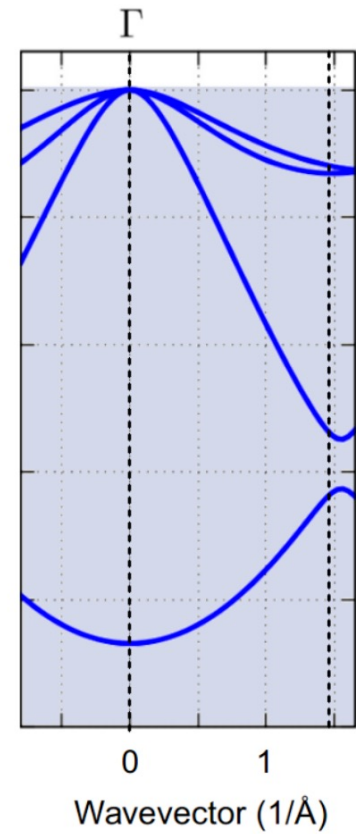
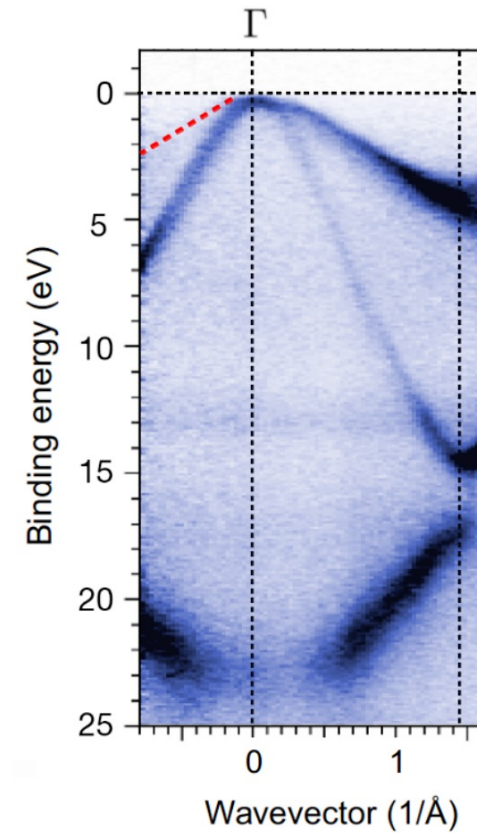
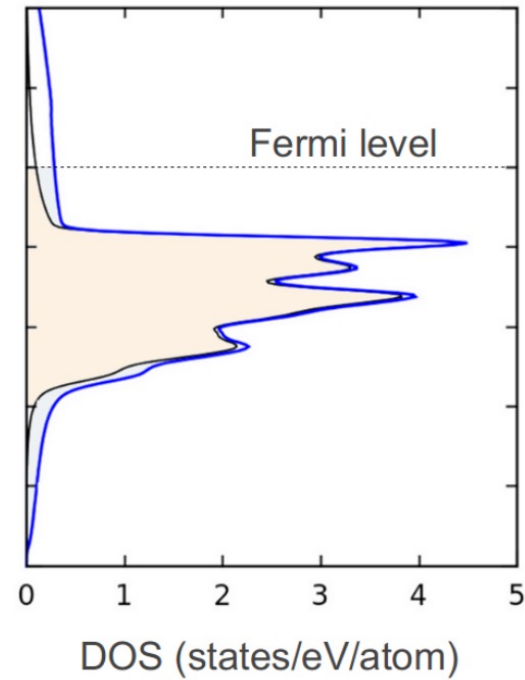
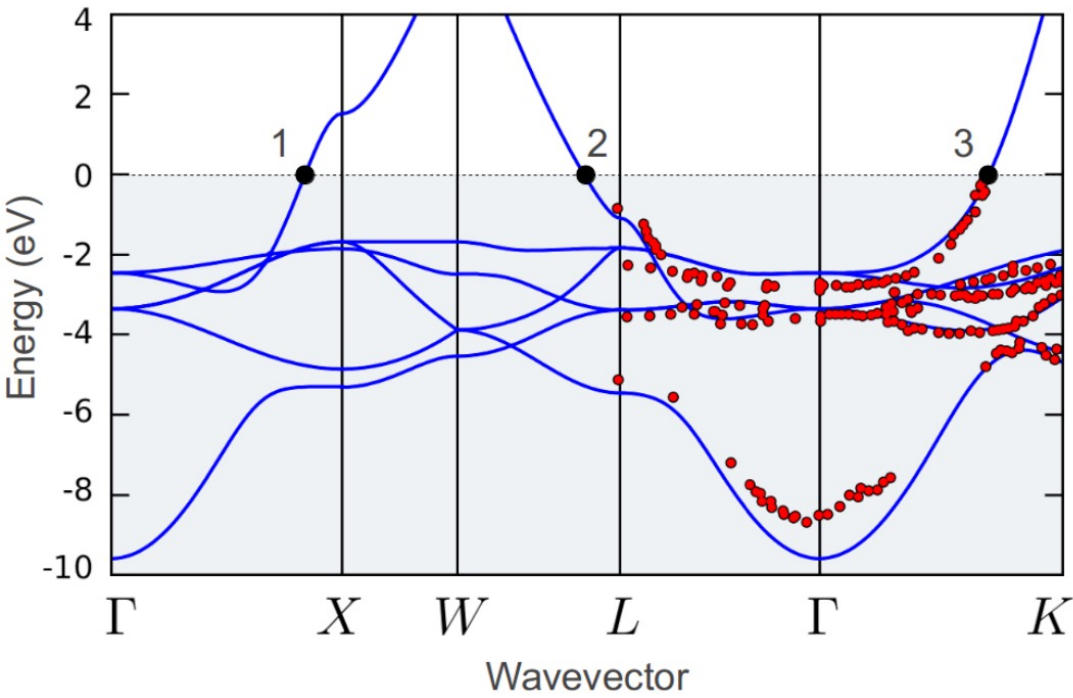
Pseudopotential

$$\left[-\frac{1}{2}\nabla^2 + V_n(\mathbf{r}) + V_H(\mathbf{r}) + V_{xc}(\mathbf{r}) \right] \phi_i(\mathbf{r}) = \varepsilon_i \phi_i(\mathbf{r}).$$



Norm-conserved Pseudopotential
 Ultrasoft Pseudopotential
 Projector Augmented Wave

Total Energy and Eigenfunctions



Taylor Expansion of the Total Energy

What are we going to do with the energy?

$$E(u, \mathcal{E}, \eta) = E_0 +$$

Taylor Expansion of the Total Energy

$$E(u, \mathcal{E}, \eta) = E_0 +$$

$$\frac{\partial E}{\partial u_m} u_m + \frac{\partial E}{\partial \mathcal{E}_\alpha} \mathcal{E}_\alpha + \frac{\partial E}{\partial \eta_j} \eta_j +$$

Forces
Polarization
Stress

$$\frac{1}{2} \frac{\partial^2 E}{\partial u_m \partial u_n} u_m u_n + \frac{1}{2} \frac{\partial^2 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta} \mathcal{E}_\alpha \mathcal{E}_\beta + \frac{1}{2} \frac{\partial^2 E}{\partial \eta_i \partial \eta_j} \eta_i \eta_j + \frac{1}{2} \frac{\partial^2 E}{\partial u_m \partial \mathcal{E}_\alpha} u_m \mathcal{E}_\alpha + \frac{1}{2} \frac{\partial^2 E}{\partial u_m \partial \eta_j} u_m \eta_j + \frac{1}{2} \frac{\partial^2 E}{\partial \mathcal{E}_\alpha \partial \eta_j} \mathcal{E}_\alpha \eta_j +$$

Harmonic force constants
Dielectric susceptibility
Elastic moduli
Born-effective charges
Force response of the internal strain tensor
Piezoelectric strain tensor

$$\frac{1}{6} \frac{\partial^3 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta \partial \mathcal{E}_\gamma} \mathcal{E}_\alpha \mathcal{E}_\beta \mathcal{E}_\gamma + \frac{1}{6} \frac{\partial^3 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta \partial u_m} \mathcal{E}_\alpha \mathcal{E}_\beta u_m + \frac{1}{6} \frac{\partial^3 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta \partial \eta_i} \mathcal{E}_\alpha \mathcal{E}_\beta \eta_i + \dots$$

Nonlinear susceptibility
Raman susceptibility matrix elements
Elasto-optic tensor

Taylor Expansion of the Total Energy

$$E(u, \mathcal{E}, \eta) = E_0 +$$

$$\frac{\partial E}{\partial u_m} u_m + \frac{\partial E}{\partial \mathcal{E}_\alpha} \mathcal{E}_\alpha + \frac{\partial E}{\partial \eta_j} \eta_j +$$

Hellmann-Feynman Modern Theory of Polarization Stress Theorem

$$\frac{1}{2} \frac{\partial^2 E}{\partial u_m \partial u_n} u_m u_n + \frac{1}{2} \frac{\partial^2 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta} \mathcal{E}_\alpha \mathcal{E}_\beta + \frac{1}{2} \frac{\partial^2 E}{\partial \eta_i \partial \eta_j} \eta_i \eta_j + \frac{1}{2} \frac{\partial^2 E}{\partial u_m \partial \mathcal{E}_\alpha} u_m \mathcal{E}_\alpha + \frac{1}{2} \frac{\partial^2 E}{\partial u_m \partial \eta_j} u_m \eta_j + \frac{1}{2} \frac{\partial^2 E}{\partial \mathcal{E}_\alpha \partial \eta_j} \mathcal{E}_\alpha \eta_j +$$

DFPT DFPT Finite electric field DFPT DFPT Finite electric field DFPT DFPT Finite electric field

$$\frac{1}{6} \frac{\partial^3 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta \partial \mathcal{E}_\gamma} \mathcal{E}_\alpha \mathcal{E}_\beta \mathcal{E}_\gamma + \frac{1}{6} \frac{\partial^3 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta \partial u_m} \mathcal{E}_\alpha \mathcal{E}_\beta u_m + \frac{1}{6} \frac{\partial^3 E}{\partial \mathcal{E}_\alpha \partial \mathcal{E}_\beta \partial \eta_i} \mathcal{E}_\alpha \mathcal{E}_\beta \eta_i + \dots$$

2n+1 theorem Finite electric field 2n+1 theorem Finite electric field 2n+1 theorem Finite electric field

Finite difference method

$$p_{ij\mu\nu} \approx \frac{\Delta(\varepsilon_{ij}^{-1})(\eta^+) - \Delta(\varepsilon_{ij}^{-1})(\eta^-)}{2\eta_{\mu\nu}} + \mathcal{O}(\eta^2).$$

First-Principles Study of Pockels Effect in Tetragonal BaTiO₃

Inhwan Kim

Department of Physics, The University of Texas at Austin

2023 November 13th PMA 11.176

Magnetic Property



Contents lists available at ScienceDirect

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journal homepage: www.elsevier.com/locate/jalcom



Large enhancement of magnetic moment in nitrated CeFe_{12}

Joonhyuk Lee^a, Sangkyun Ryu^a, Inhwan Kim^a, Mirang Byeon^b, Myung-Hwan Jeong^c, Jae S. Lee^c, Tae Eun Hong^b, Jinhyung Cho^d, Jaekwang Lee^{a,*}, Jun Kue Park^{c,*}, Hyoungeen Jeon^{a,e,*}

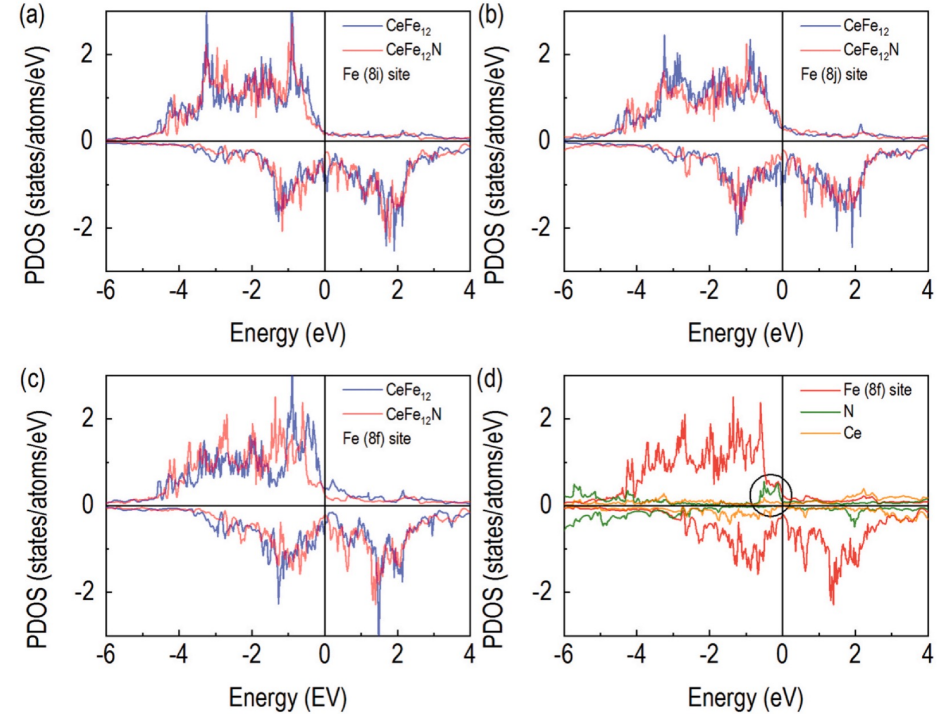
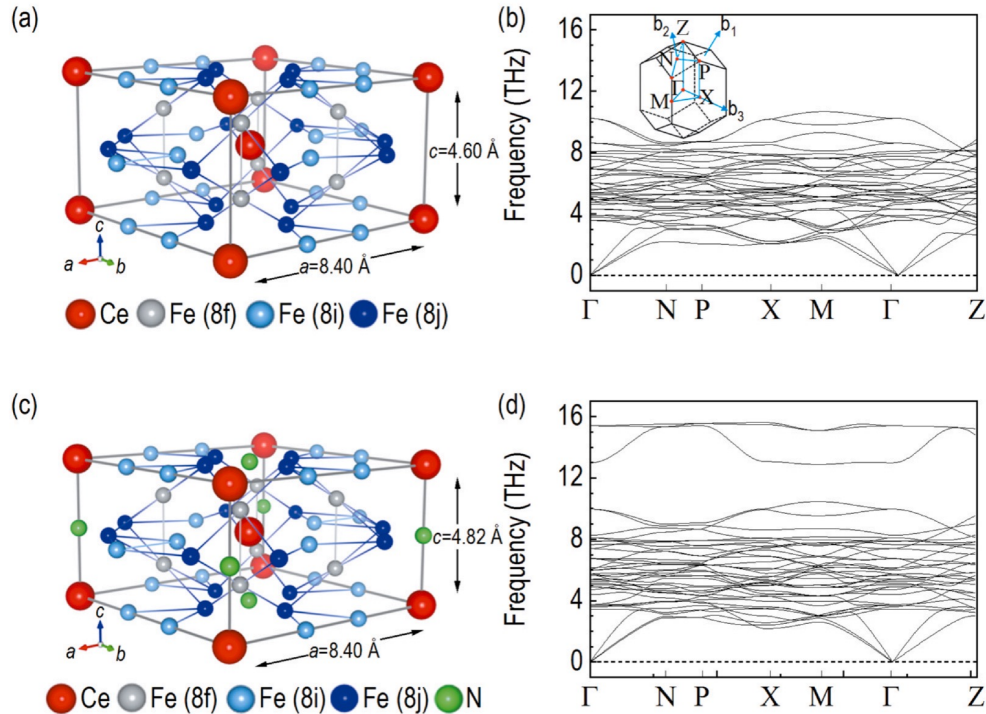
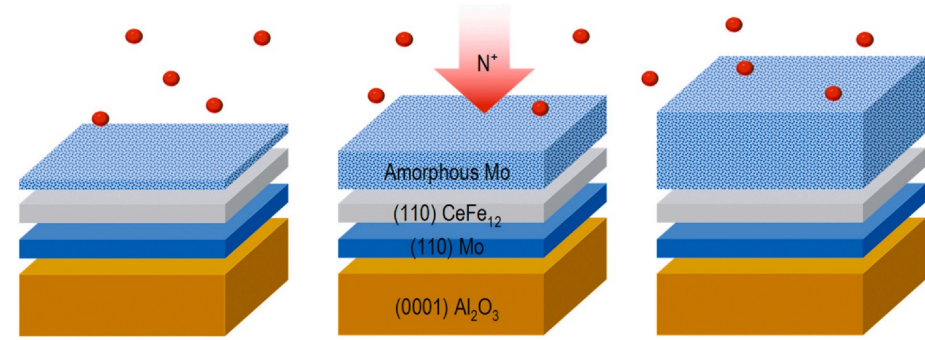
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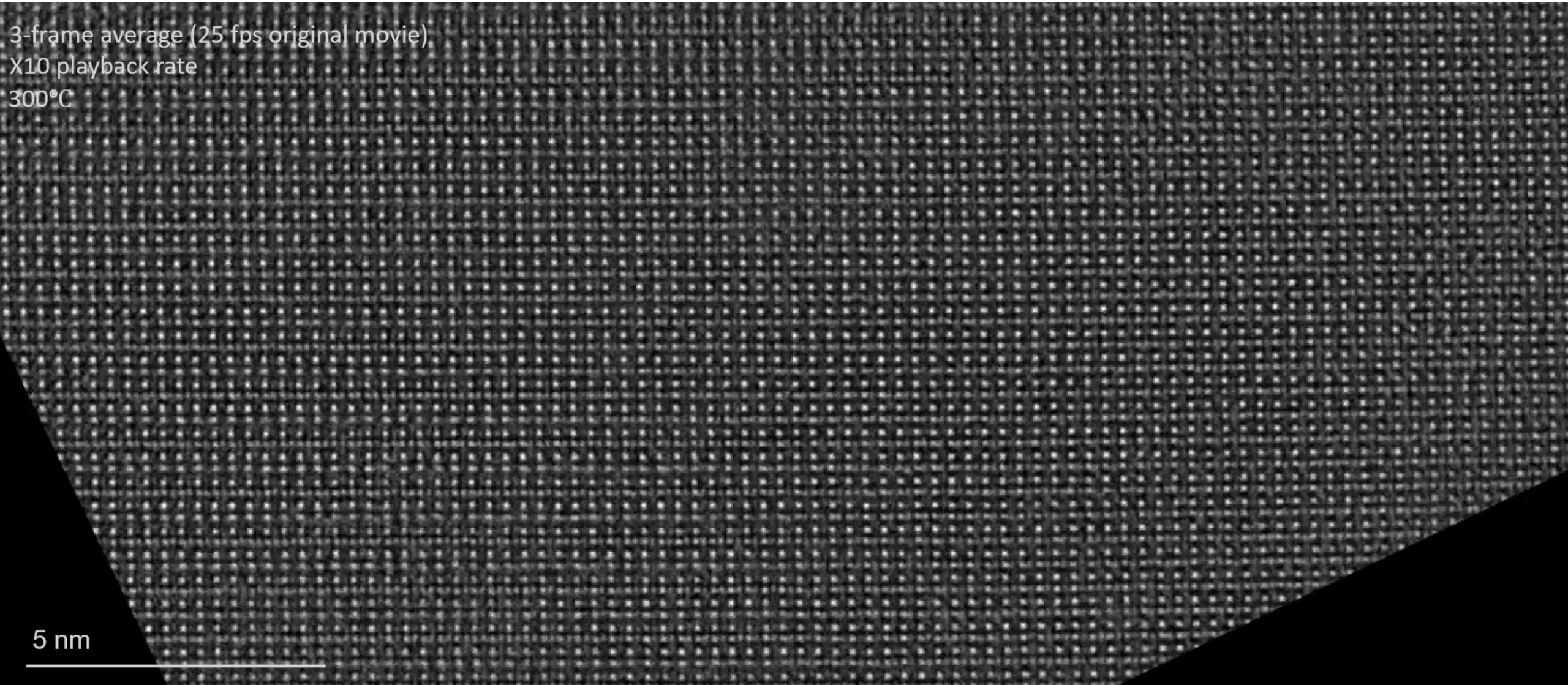


Dynamics at a phase boundary

3-frame average (25 fps original movie)

X10 playback rate

300°C



5 nm

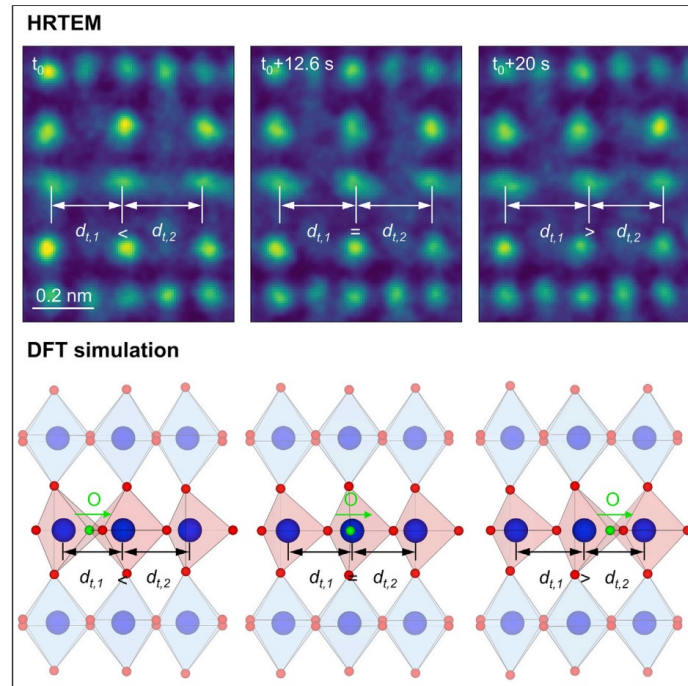
Dynamics at a phase boundary

Matter



Article

Atomic-scale operando observation of oxygen diffusion during topotactic phase transition of a perovskite oxide



Yaolong Xing, Inhwan Kim, Kyeong Tae Kang, ..., Woo Seok Choi, Jaekwang Lee, Sang Ho Oh

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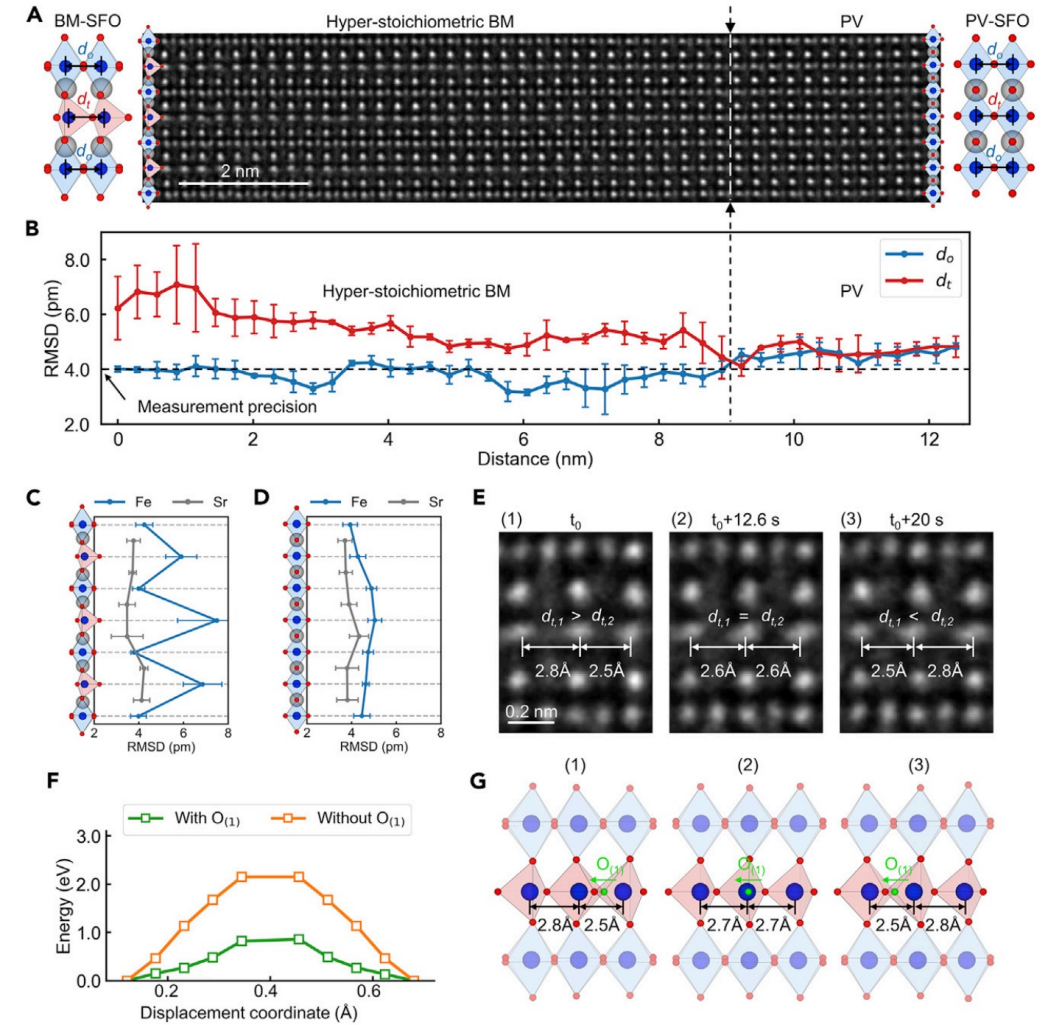
Highlights

Operando atomic-scale imaging of oxygen diffusion during SrFeO₃-SrFeO_{2.5} transition

Hyper-stoichiometric SrFeO_{2.5} with excess oxygen emerging at phase boundary

Oxygen diffusion along FeO₄ chains via modification of oxygen coordination



Steady-state diffusion via interstitialcy diffusion across fast-diffusion channels




Linear Electro-Optic response

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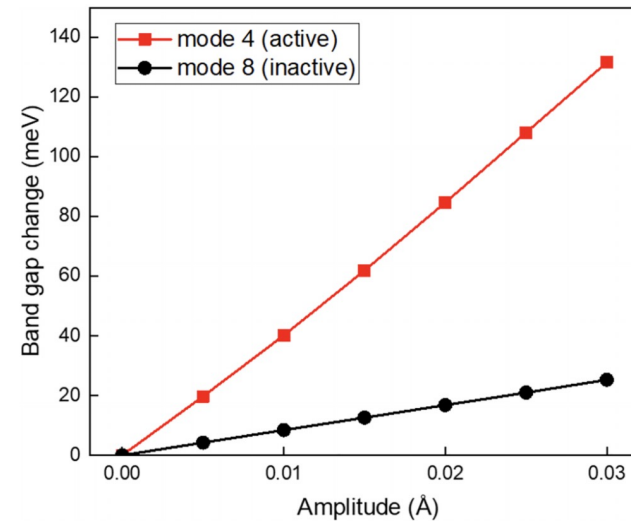
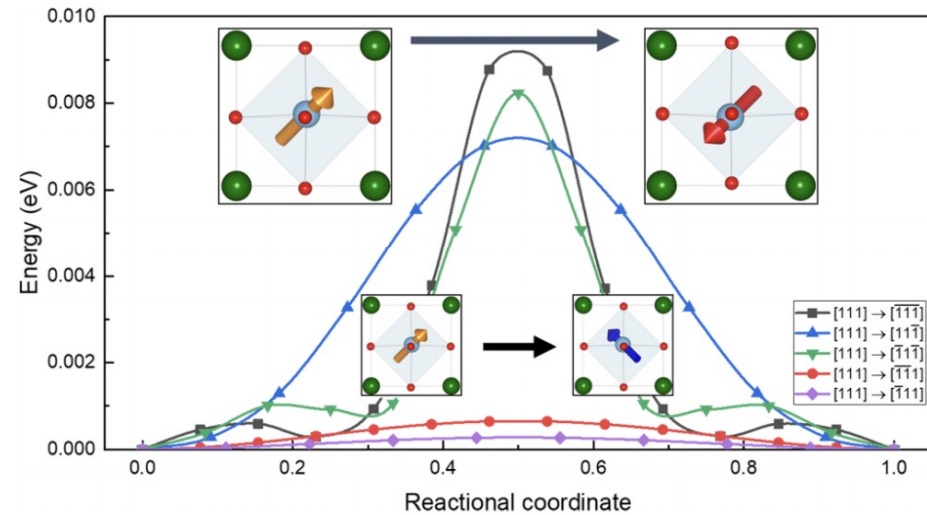
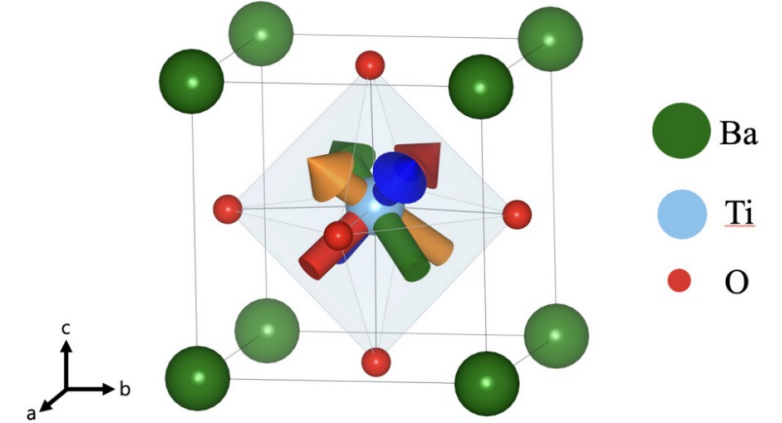
Nature of electro-optic response in tetragonal BaTiO₃

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Barium titanate, BaTiO₃ (BTO), has emerged as a promising electro-optic material with applications in silicon photonics. It boasts one of the largest known electro-optic coefficients; however, the origin of this giant electro-optic response has not been investigated in detail and is poorly understood. Here we report on a first-principles study of the electro-optic or Pockels tensor in tetragonal *P4mm* BTO. We find good agreement with experiment if the *P4mm* structure is viewed as a dynamic average of four lower symmetry *Cm* structures. The large value of the Raman component of the EO coefficient is attributed to a low frequency and strong electron-phonon coupling of the lowest optical mode, and we trace the equally large piezoelectric contribution to the large components of the piezoelectric and elasto-optic tensors.

$$= 8\pi\chi_{ij\gamma}^{(2)} + 4\pi \sum_m \frac{1}{\omega_m^2} \left(\sum_{\kappa,\alpha} \frac{\partial\chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial\tau_{\kappa\alpha}} u_m(\kappa\alpha) \right) \times \left(\sum_{\kappa',\beta} Z_{\kappa',\gamma\beta}^* u_m(\kappa'\beta) \right) + p_{ij\mu\nu} d_{\gamma\mu\nu}$$



Electronic Pockels Tensor (pm/V)			Ionic Pockels Tensor (pm/V)		
0	0	0.7	1.8	0.5	-25
0	0	0.7	-1.8	0.25	-25
0	0	2	0	0	41
0	0.76	0	0.25	823	0
0.76	0	0	816	0.5	0
0	0	0	0	0	0

Linear Electro-Optic response

Galactic Axion Laser Interferometer Leveraging Electro-Optics: GALILEO

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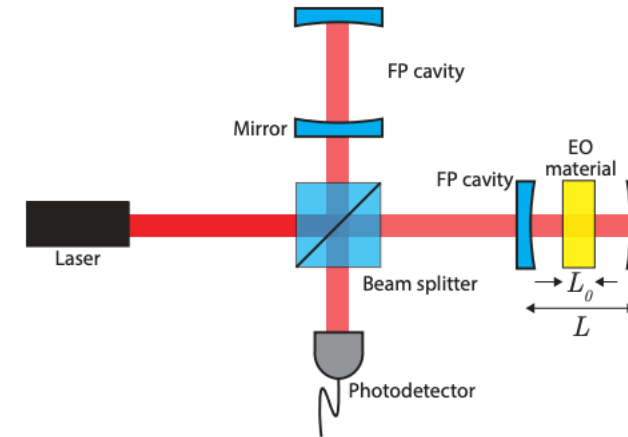
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(Dated: June 6, 2023)

We propose a novel experimental method for probing light dark matter candidates. We show that an electro-optical material's refractive index is modified in the presence of a coherently oscillating dark matter background. A high-precision resonant Michelson interferometer can be used to read out this signal. The proposed detection scheme allows for the exploration of an uncharted parameter space of dark matter candidates over a wide range of masses – including masses exceeding a few tens of microelectronvolts, which is a challenging parameter space for microwave cavity haloscopes.



$$\delta n \sim \begin{cases} 1.8 \times 10^{-10} \text{ (m/V) } E_{\text{DM}}, & \text{for LiNbO}_3 \\ 6.4 \times 10^{-9} \text{ (m/V) } E_{\text{DM}}, & \text{for BaTiO}_3 \end{cases}$$

And hopefully paper 4 and 5 this year...

MJ10240 - Multiferroism in strained strontium hexaferrite epitaxial thin films

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Detailed Status Information

Manuscript #	NCHEM-23081722
Current Revision #	0
Submission Date	21st August 23
Current Stage	Manuscript under consideration
Title	Formation Mechanism of Infinite-Layer Transition Metal Oxide
Manuscript Type	Article

Outline of the Qualifier Presentation

- Linear electro-optic effect and Silicon photonics
- Tetragonal BaTiO_3 as a promising EO material
- Structural consideration
- Clamped Pockels tensor – Ionic contribution
- Unclamped Pockels tensor – Piezo contribution

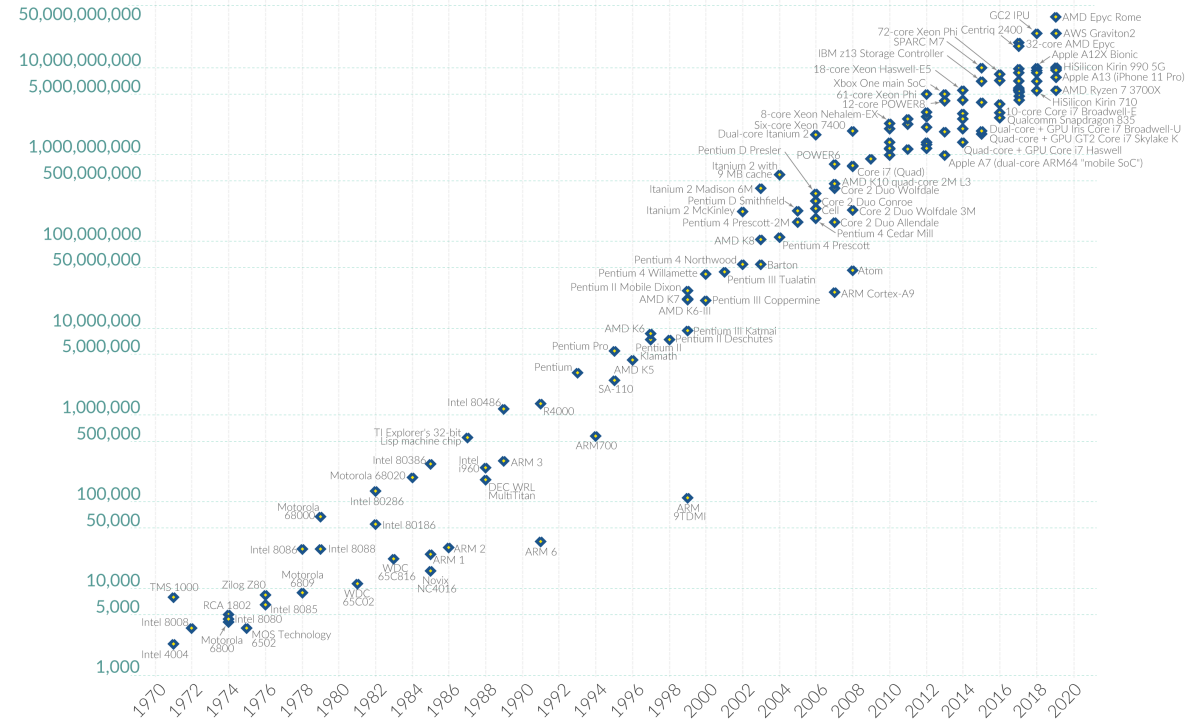
Introduction: Silicon Photonics

Moore's Law: The number of transistors on microchips doubles every two years

Moore's law describes the empirical regularity that the number of transistors on integrated circuits doubles approximately every two years. This advancement is important for other aspects of technological progress in computing – such as processing speed or the price of computers.

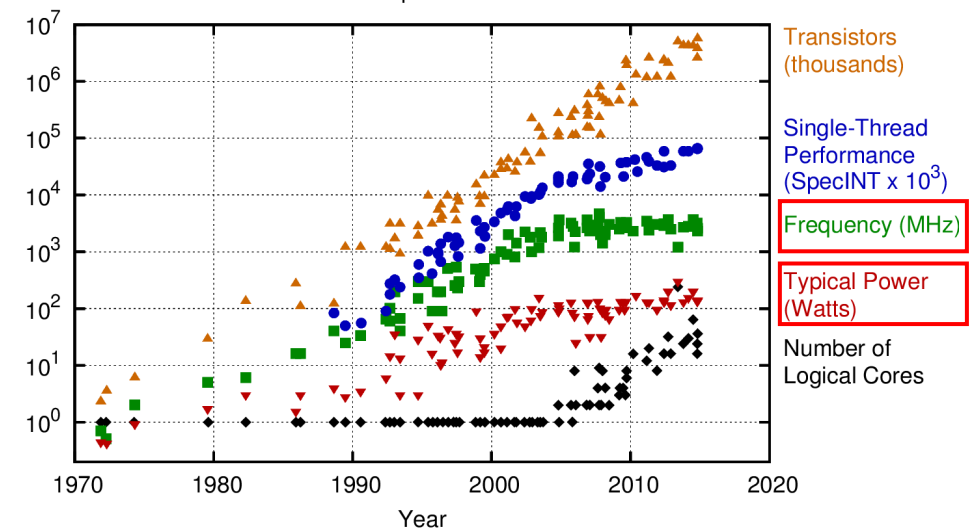


Transistor count

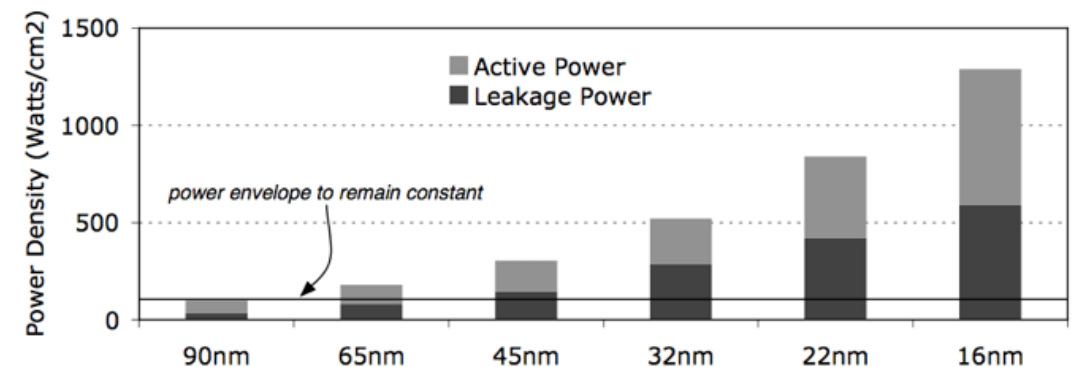


Data source: Wikipedia (wikipedia.org/wiki/Transistor_count) Year in which the microchip was first introduced
 OurWorldinData.org – Research and data to make progress against the world's largest problems. Licensed under CC-BY by the authors Hannah Ritchie and Max Roser.

40 Years of Microprocessor Trend Data



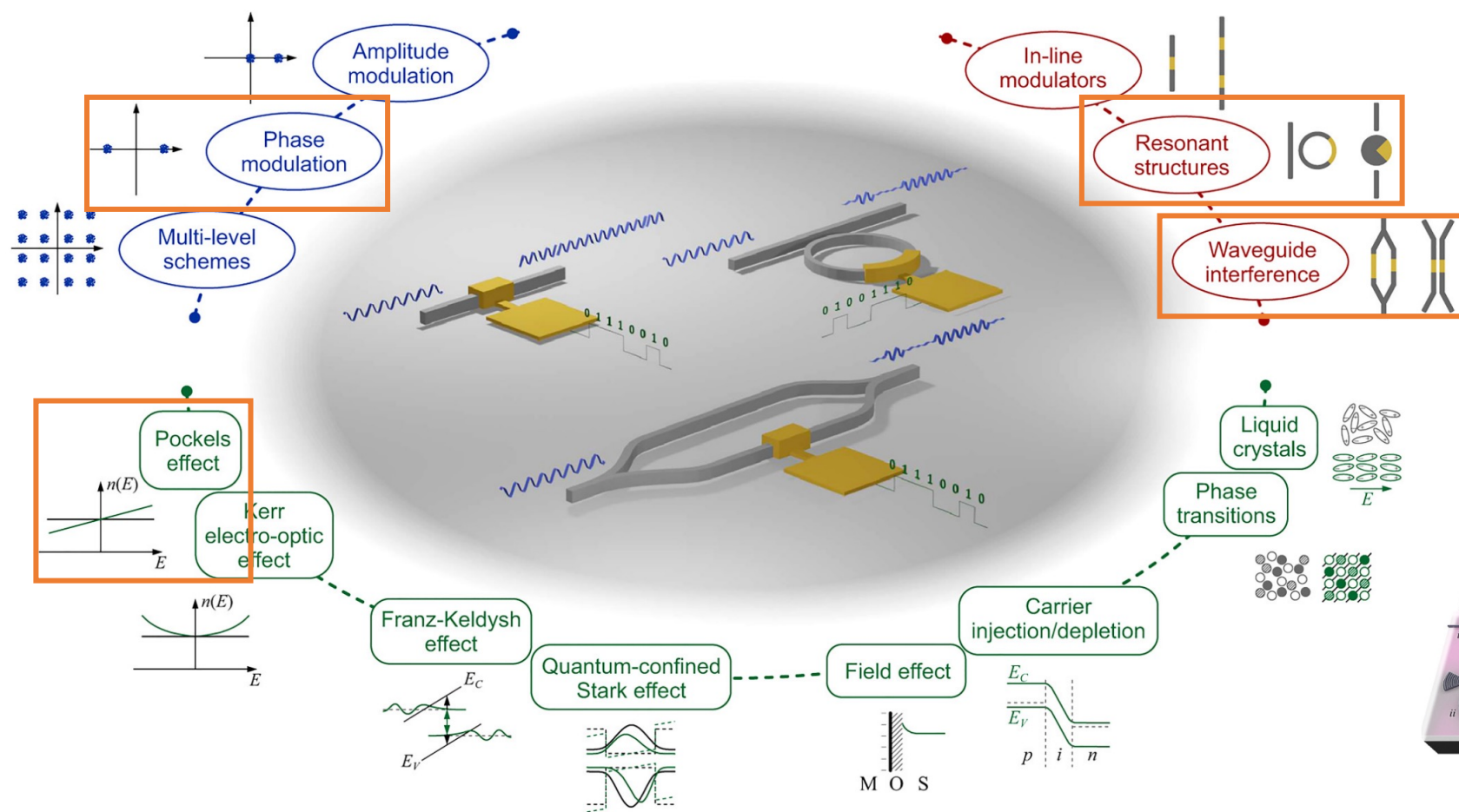
Original data up to the year 2010 collected and plotted by M. Horowitz, F. Labonte, O. Shacham, K. Olukotun, L. Hammond, and C. Batten
 New plot and data collected for 2010-2015 by K. Rupp



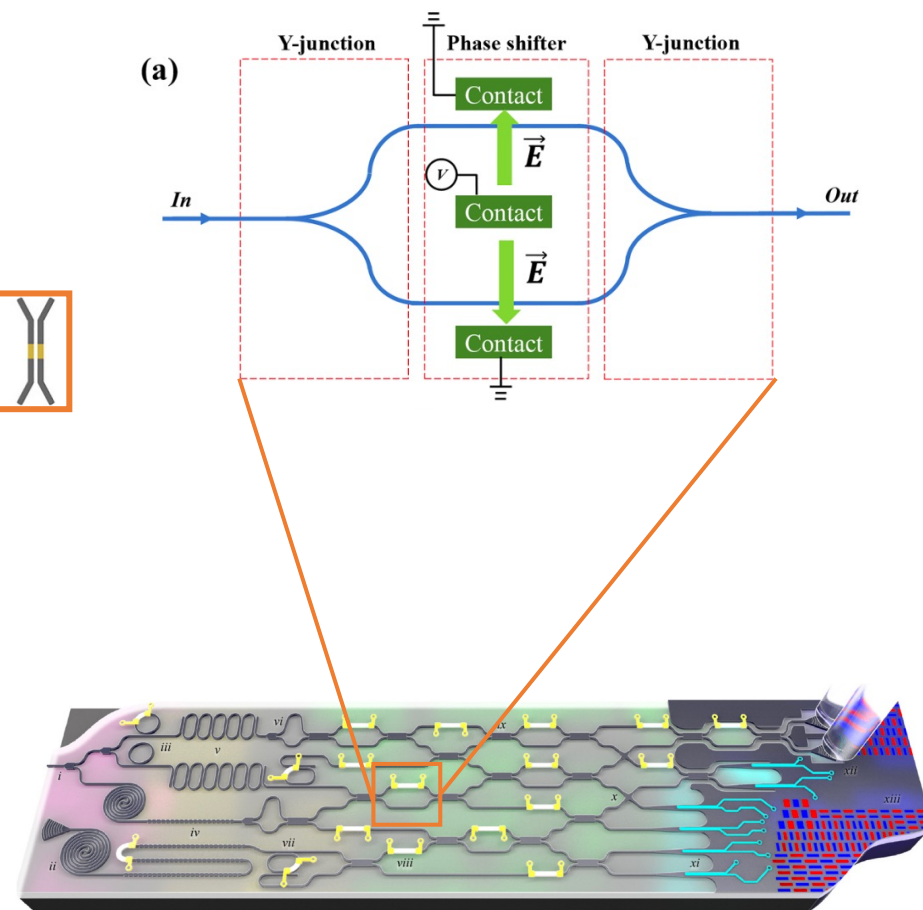
Source: Shekhar Borkar (Intel)

- Moore's law is still working!
- However, both power dissipation and clock speed are currently limiting factors.

Introduction: Silicon Photonics

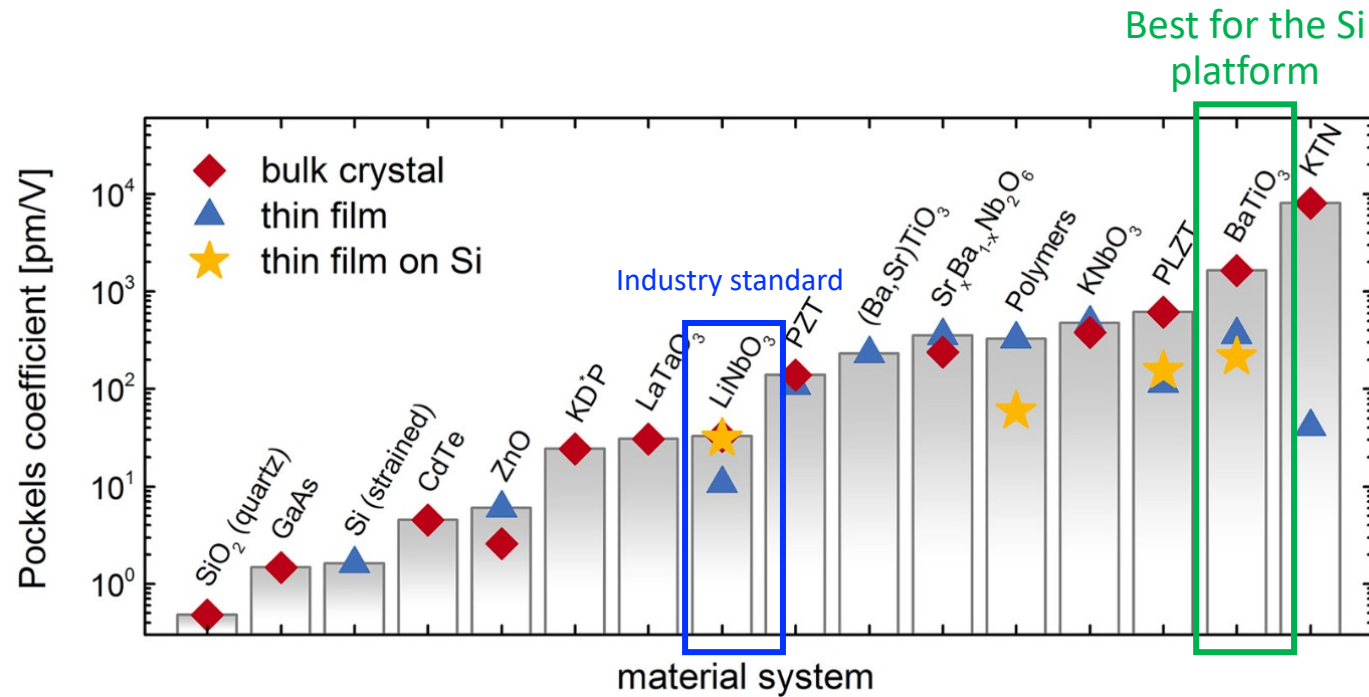


Mach-Zehnder interferometer

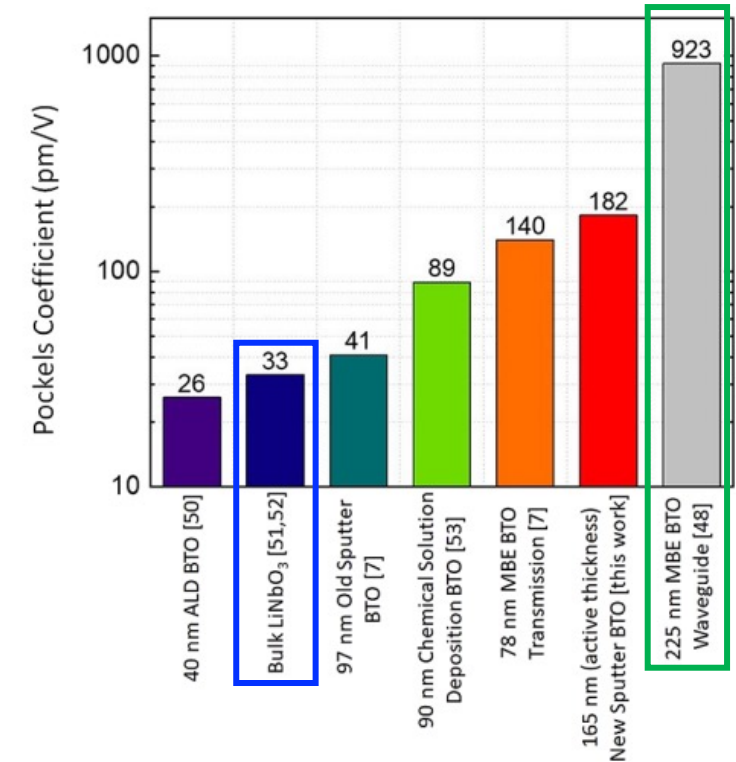


Optical computing in silicon

Introduction: Electro-Optically Active Materials



For BTO system



- Bulk tetragonal BaTiO₃ is one of the best candidates for the EO material for Si photonics platform
- More theoretical studies are needed to understand the electro-optic properties of BTO

Introduction: Ferroelectric

Displacive type
 BaTiO_3

Order-disorder type
 LiNbO_3

- Linear electro-optic effect is only allowed in a crystal without inversion symmetry
- More theoretical studies are needed to understand the electro-optic properties of BTO

Computational Details

DFT and DFPT calculation:

LDA exchange-correlation with norm-conserving pseudopotentials

For non-linear term, $2n+1$ theorem with PEAD formulation

12x12x12 k-point

1000 eV energy cut off

10^{-5} eV/Angstrom

3x3x3 supercell

3x3x3 k-point

Nudged elastic band (NEB) calculation

LO-TO splitting (non-analytical term) is considered



Self-consistent phonon

Harmonic phonon:

the force acting on atom l to $alpha$ direction when atom m is moved along $beta$ direction and all the other atoms are fixed.

$$\Phi_{\alpha\beta}(lm)$$

In contrast, self-consistent phonon:

the force acting on atom l should rather be derived by regarding the other atoms as moving. This gives rise to the notion of an effective restoring force. It is defined as a thermodynamical average of the restoring forces, taken over all configurations of the other atoms and weighted with the probability of each configurations.

SCHA is formally again harmonic, the true lattice system is to be approximated by some other effective harmonic lattice whose force constants and lattice parameter are to be optimally adjusted.

The renormalized force constants are obtained from a **self-consistency** condition. Self-consistency is achieved by replacing the normal harmonic force constants by *effective* force constants which are thermal averages with respect to the *effective* harmonic Hamiltonian.

The Linear Electro-Optic Response: the Pockels Effect

$$\Delta \left(\frac{1}{n^2} \right) = \Delta (\varepsilon^{-1})_{ij} = \sum_{\gamma} r_{ij\gamma} E_{\gamma}$$

$$\Delta (\varepsilon^{-1})_{ij} = -\varepsilon_{im}^{(-1)} \Delta \varepsilon_{mn} \varepsilon_{nj}^{(-1)}$$

The Linear Electro-Optic Response: the Pockels Effect

$$\Delta \left(\frac{1}{n^2} \right) = \Delta (\varepsilon^{-1})_{ij} = \sum_{\gamma} \underline{r_{ij\gamma}} E_{\gamma}$$

γ Pockels tensor

$$\Delta (\varepsilon^{-1})_{ij} = -\varepsilon_{im}^{(-1)} \Delta \varepsilon_{mn} \varepsilon_{nj}^{(-1)}$$

$$\begin{aligned} \left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_{\gamma}} \right]_{\mathbf{R}_0, \eta_0, E=0} &= \left[\frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{\partial E_{\gamma}} \right]_{E=0} + \left[\frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{\partial \tau_{\kappa\alpha}} \right]_{\mathbf{R}_0} \frac{\partial \tau_{\kappa\alpha}}{\partial E_{\gamma}} + \left[\frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{\partial \eta_{\mu\nu}} \right]_{\eta_0} \frac{\partial \eta_{\mu\nu}}{\partial E_{\gamma}} \\ &= 8\pi \chi_{ij\gamma}^{(2)} + 4\pi \sum_m \frac{1}{\omega_m^2} \left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right) \times \left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right) + \underline{p_{ij\mu\nu}} d_{\gamma\mu\nu} \\ &\quad \text{Phonon} \quad \text{Raman susceptibility tensor} \quad \text{Mode polarity} \quad \text{Piezoelectric tensor} \\ &\quad \text{Elasto-optic tensor} \\ &= \underline{r_{ij\gamma}^{elec}} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}. \\ &\quad \text{Unclamped EO tensor} \end{aligned}$$

The Linear Electro-Optic Response: the Pockels Effect

Electric enthalpy is defined as,

$$F(\mathbf{r}, \eta, \mathbf{E}) = F(\mathbf{r}, \eta, \mathbf{E} = 0) - \Omega_0 P_i(\mathbf{R}, \eta) E_i - \frac{\Omega_0}{8\pi} \varepsilon_{ij}(\mathbf{R}, \eta) E_i E_j - \frac{\Omega_0}{3} \chi_{ijk}^{(2)}(\mathbf{R}, \eta) E_i E_j E_k + \dots$$

$$\frac{\partial F}{\partial \tau_{\kappa\alpha}} = 0 \quad \text{: The equilibrium condition of electric enthalpy F}$$

$$= \left. \frac{\partial F(\mathbf{R}, \eta_0, \mathbf{E} = 0)}{\partial \tau_{\kappa\alpha}} \right|_{\mathbf{R}(E)} - \Omega_0 \left. \frac{\partial P_i(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} \right|_{\mathbf{R}(E)} E_i - \frac{\Omega_0}{8\pi} \left. \frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} \right|_{\mathbf{R}(E)} E_i E_j + \dots$$

$$\left. \frac{\partial^2 F(\mathbf{R}, \eta_0, \mathbf{E} = 0)}{\partial \tau_{\kappa\alpha} \partial \tau_{\kappa'\alpha'}} \right|_{\mathbf{R}_0} \frac{\partial \tau_{\kappa'\alpha'}}{\partial E_\gamma} = \Omega_0 \left. \frac{\partial P_\gamma(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} \right|_{\mathbf{R}_0} \quad \tau_{\kappa\alpha} = \tau_m u_m(\kappa\alpha) \quad \longrightarrow \quad \boxed{\frac{\partial \tau_m}{\partial E_\gamma} = \frac{1}{\omega_m^2} \sum_{\kappa,\alpha} Z_{\kappa,\gamma\alpha}^* u_m(\kappa\alpha)}$$

The Linear Electro-Optic Response: the Pockels Effect

$$\begin{aligned}
 \left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_\gamma} \right]_{\mathbf{R}_0, \eta_0, E=0} &= 8\pi\chi_{ij\gamma}^{(2)} + 4\pi \underbrace{\sum_m \frac{1}{\omega_m^2}}_{\text{Phonon}} \left(\underbrace{\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha)}_{\text{Raman susceptibility tensor}} \right) \times \left(\underbrace{\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta)}_{\text{Mode polarity}} \right) + \underbrace{p_{ij\mu\nu} \overline{d_{\gamma\mu\nu}}}_{\text{Piezoelectric tensor}} \\
 &\quad \underbrace{\hspace{10em}}_{\text{Elasto-optic tensor}} \\
 &= \underbrace{r_{ij\gamma}^{elec} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}}_{\text{Unclamped EO tensor}}.
 \end{aligned}$$

Phonon part

$$4\pi \sum_m \frac{1}{\omega_m^2}$$

Phonon

$$\underline{u_m(\kappa\alpha)}$$

eigendisplacement

Phonon part

$$\left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_\gamma} \right]_{\mathbf{R}_0, \eta_0, E=0} = 8\pi\chi_{ij\gamma}^{(2)} + 4\pi \underbrace{\sum_m \frac{1}{\omega_m^2}}_{\text{Phonon}} \underbrace{\left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right)}_{\text{Raman susceptibility tensor}} \times \underbrace{\left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)}_{\text{Mode polarity}} + \underbrace{p_{ij\mu\nu} \overline{d_{\gamma\mu\nu}}}_{\text{Piezoelectric tensor}} + \underbrace{p_{ij\mu\nu} \overline{d_{\gamma\mu\nu}}}_{\text{Elasto-optic tensor}}$$

$$= \underbrace{r_{ij\gamma}^{elec} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}}_{\text{Unclamped EO tensor}}.$$

Raman susceptibility part

$$\left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right)$$

Raman susceptibility
tensor

Mode polarity part

$$\begin{aligned}
 \left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_\gamma} \right]_{\mathbf{R}_0, \eta_0, E=0} &= 8\pi\chi_{ij\gamma}^{(2)} + 4\pi \underbrace{\sum_m \frac{1}{\omega_m^2}}_{\text{Phonon}} \underbrace{\left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right)}_{\text{Raman susceptibility tensor}} \times \underbrace{\left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)}_{\text{Mode polarity}} + \underbrace{p_{ij\mu\nu} \overline{d_{\gamma\mu\nu}}}_{\text{Piezoelectric tensor}} \\
 &= \underbrace{r_{ij\gamma}^{elec} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}}_{\text{Unclamped EO tensor}}.
 \end{aligned}$$

Elasto-optic tensor

Piezoelectric part

$$\begin{aligned}
 \left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_\gamma} \right]_{\mathbf{R}_0, \eta_0, E=0} &= 8\pi\chi_{ij\gamma}^{(2)} + 4\pi \underbrace{\sum_m \frac{1}{\omega_m^2}}_{\text{Phonon}} \underbrace{\left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right)}_{\text{Raman susceptibility tensor}} \times \underbrace{\left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)}_{\text{Mode polarity}} + \underbrace{p_{ij\mu\nu} \overline{d}_{\gamma\mu\nu}}_{\text{Elasto-optic tensor}} \quad \text{Piezoelectric tensor} \\
 &= \underbrace{r_{ij\gamma}^{elec} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}}_{\text{Unclamped EO tensor}}.
 \end{aligned}$$

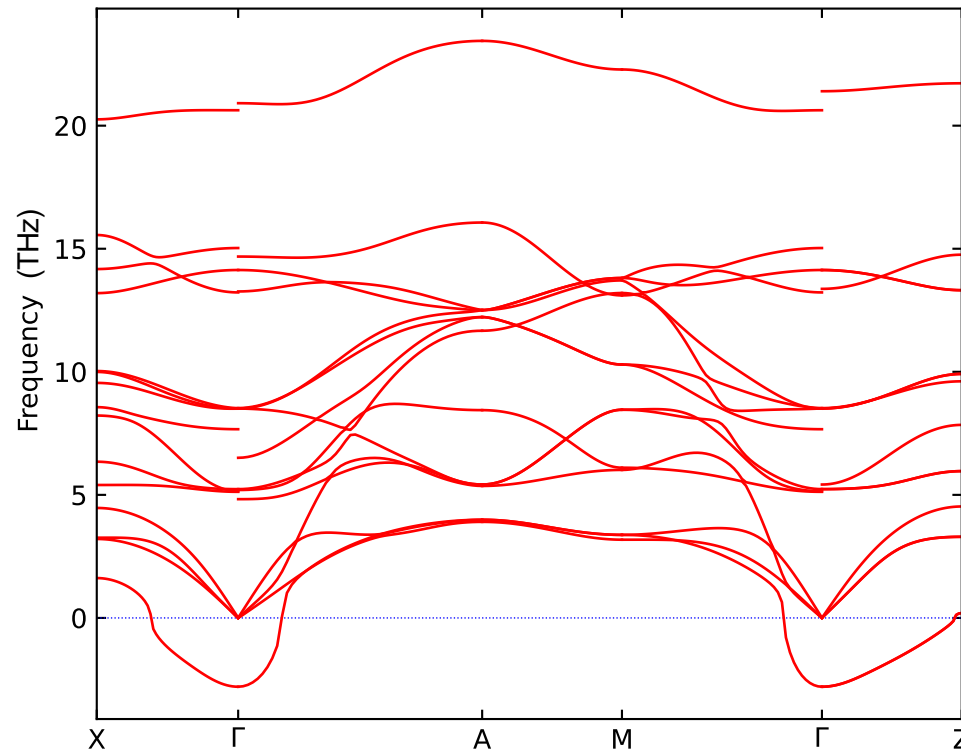
Elasto-optic part

$$\begin{aligned}
 \left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_\gamma} \right]_{\mathbf{R}_0, \eta_0, E=0} &= 8\pi\chi_{ij\gamma}^{(2)} + 4\pi \underbrace{\sum_m \frac{1}{\omega_m^2}}_{\text{Phonon}} \underbrace{\left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right)}_{\text{Raman susceptibility tensor}} \times \underbrace{\left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)}_{\text{Mode polarity}} + \underbrace{p_{ij\mu\nu} \overline{d_{\gamma\mu\nu}}}_{\text{Piezoelectric tensor}} \\
 &= \underbrace{r_{ij\gamma}^{elec} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}}_{\text{Unclamped EO tensor}}.
 \end{aligned}$$

Pockels response in rhombohedral BaTiO₃

$$4\pi \sum_m \frac{1}{\omega_m^2} \left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right) \times \left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)$$

Imaginary!

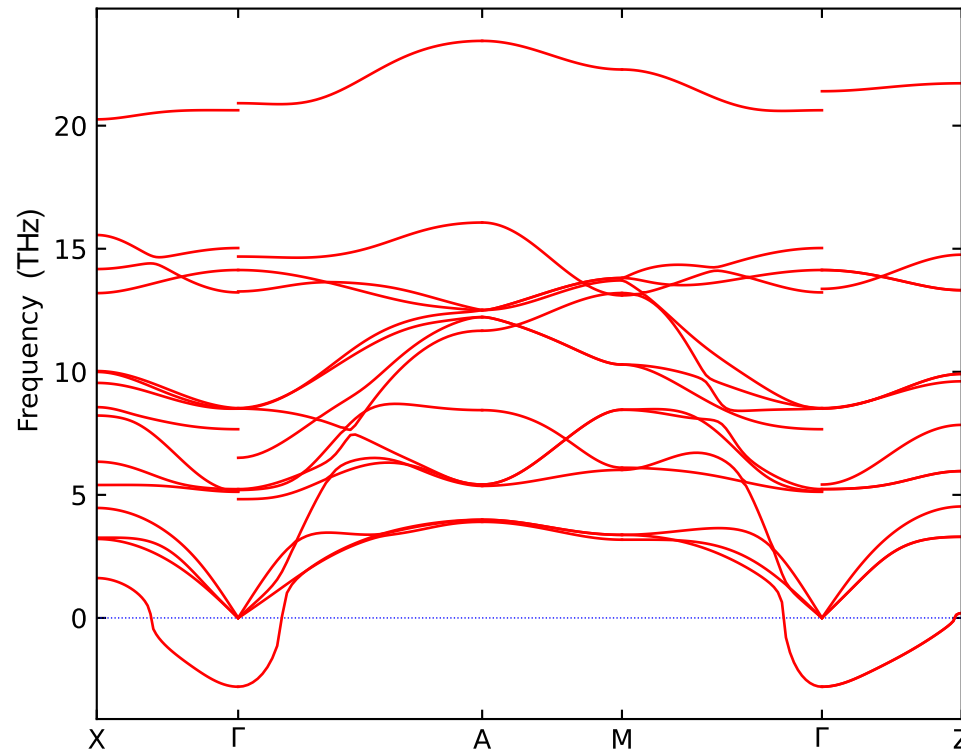


Imaginary phonon modes in the *P4mm* phase make the calculation difficult

Structural Problem: imaginary phonon mode in $P4mm$ BaTiO₃

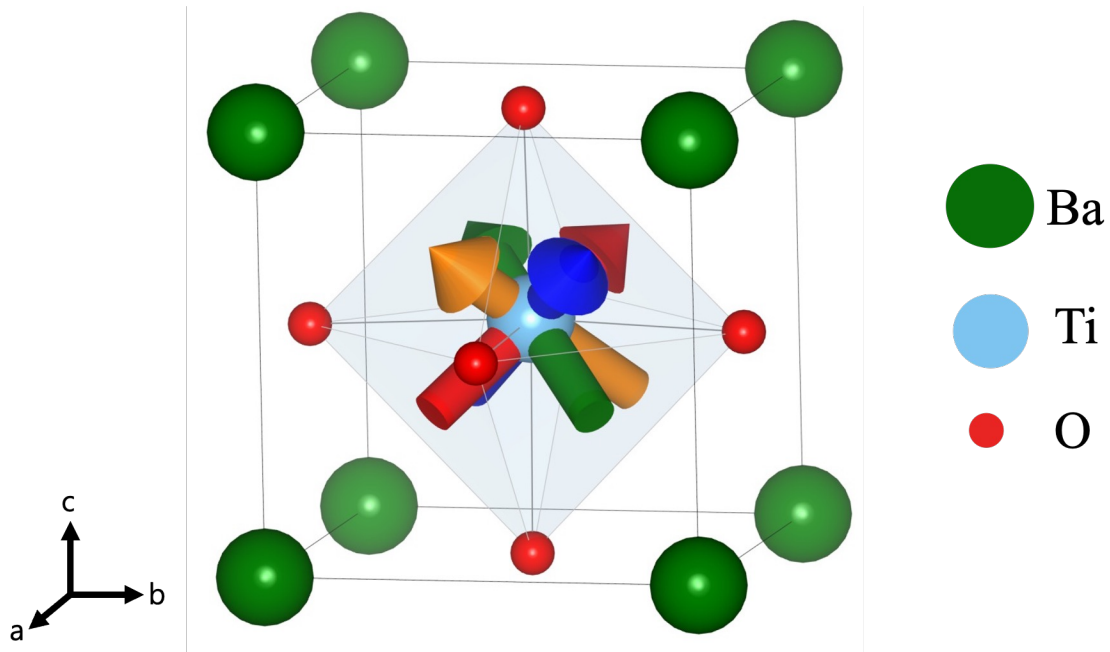
$$4\pi \sum_m \frac{1}{\omega_m^2} \left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right) \times \left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)$$

Imaginary!



Imaginary phonon modes in the $P4mm$ phase make the calculation difficult

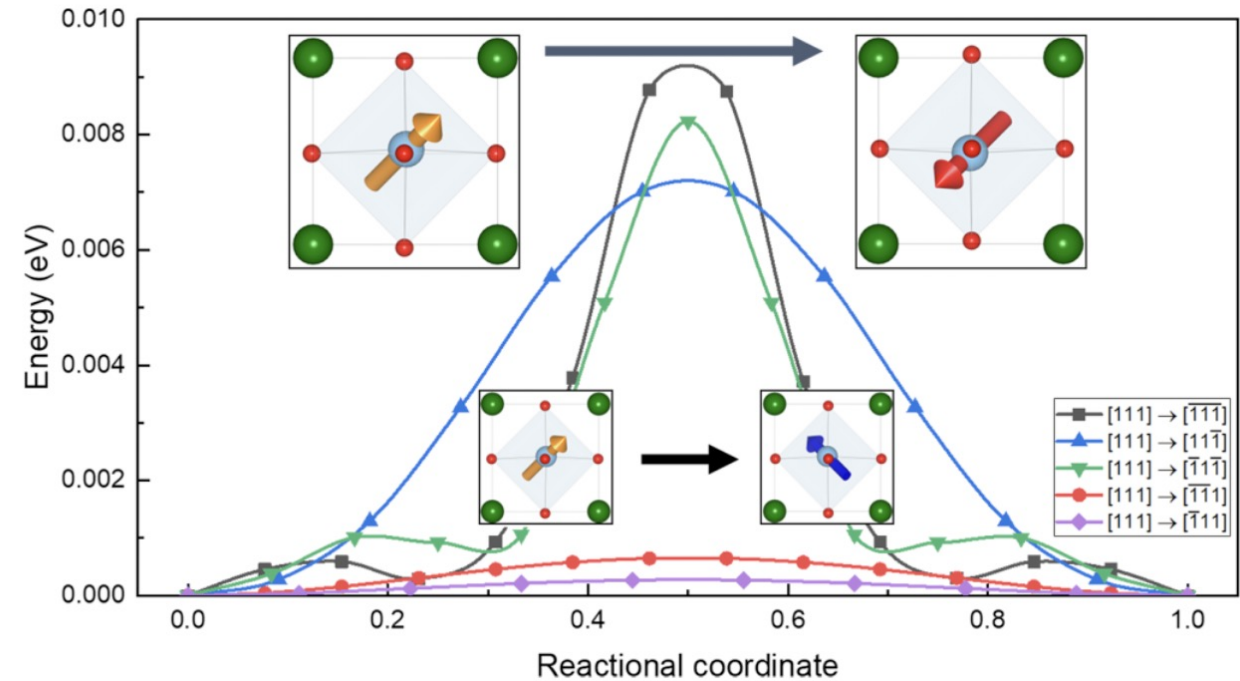
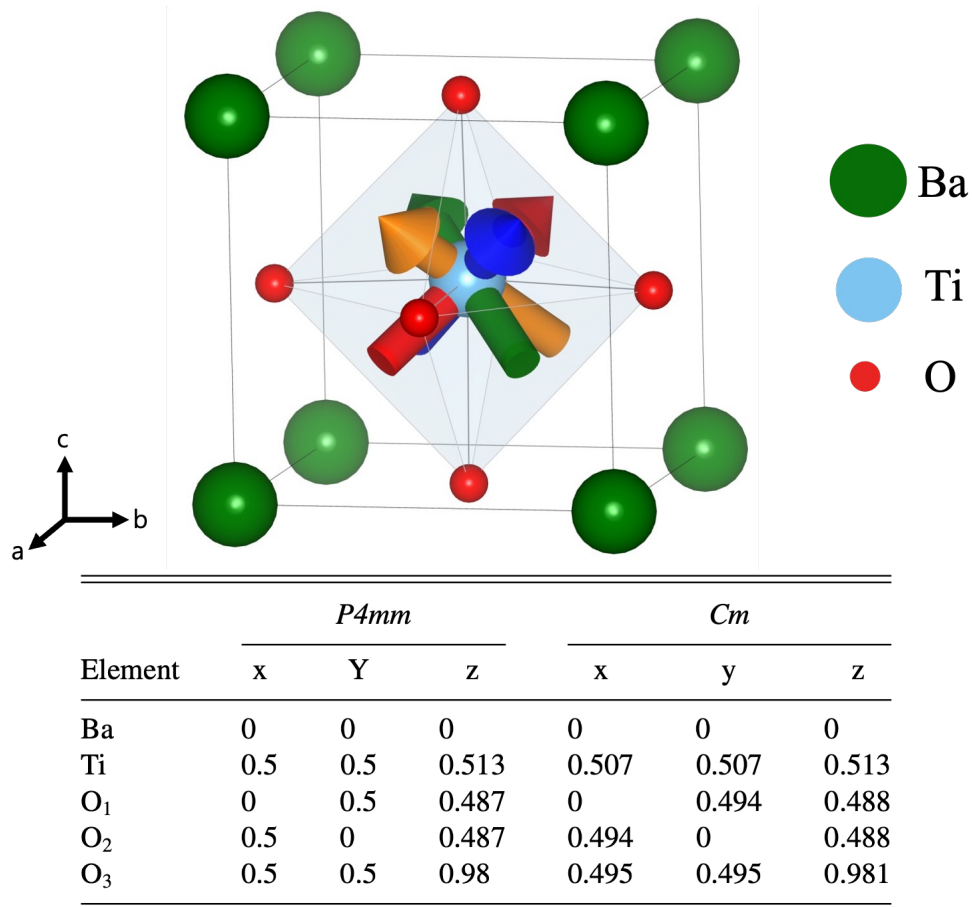
Structural Problem: $P4mm$ as average Cm structure



Other experiment results from the other presentations by Dr. Kotiuga

- In recent experiments, the high symmetry structures are microscopically averaged over low-symmetry phase
- We assume our tetragonal structure is microscopically averaged over $[111]$ -displacement.

Structural Problem: $P4mm$ as average Cm structure



- In experiments, the $P4mm$ tetragonal structure is microscopically averaged over $[111]$ -displacement.
- Energy barrier is much higher to flip the macroscopic polarization direction.

Ionic Electro-Optic Response: Phonon

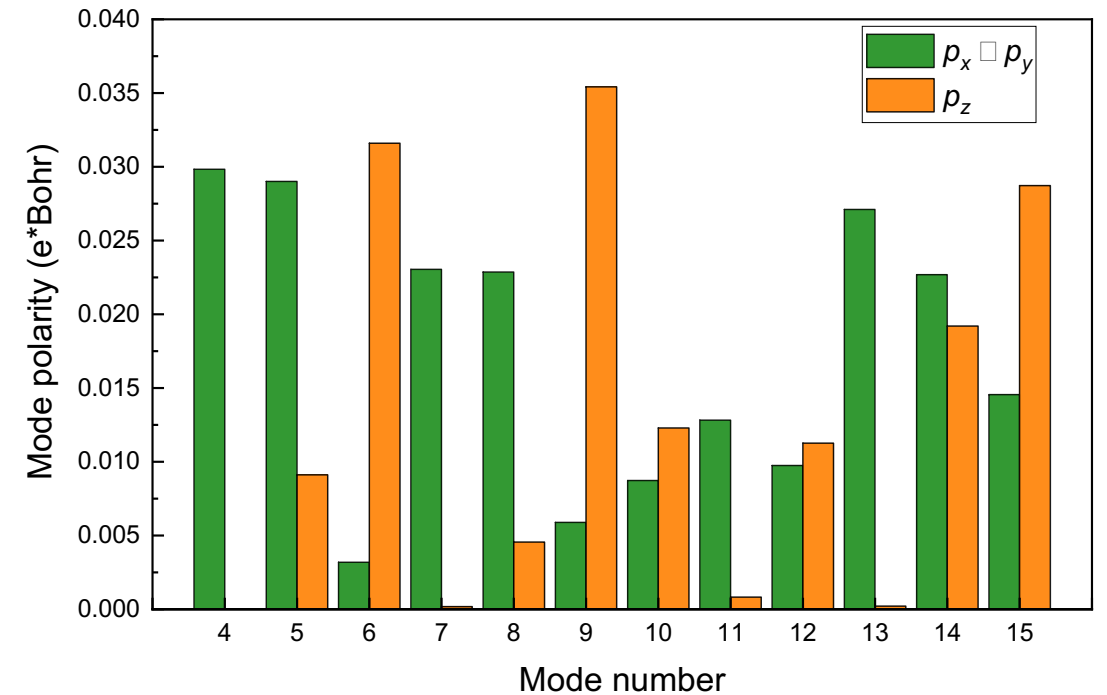
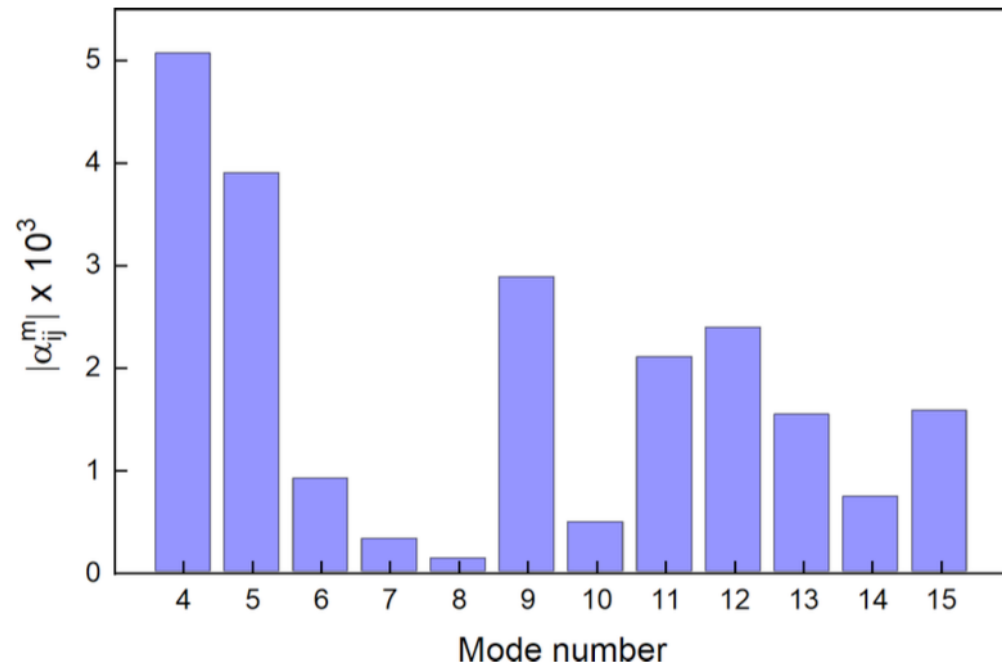
$$4\pi \sum_m \frac{1}{\omega_m^2} \left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right) \times \left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)$$

Mode Number	<i>P4mm</i> SR (cm ⁻¹)	<i>P4mm</i> LR (cm ⁻¹)	<i>Cm</i> SR (cm ⁻¹)	<i>Cm</i> LR (cm ⁻¹)	SCPH (cm ⁻¹)	Exp. [54] (cm ⁻¹)
4	-176 <i>i</i>	-176 <i>i</i>	17	57	161	34
5	-176 <i>i</i>	-176 <i>i</i>	78	170	171	180
6	164	170	170	174	174	189
7	170	170	174	175	174	
8	170	185	175	235	264	
9	287	287	236	284	281	
10	287	287	284	294	281	304
11	291	291	294	296	282	308
12	315	453	295	452	465	471
13	457	457	471	472	490	498
14	457	457	471	492	510	
15	515	718	495	674	710	725

NO imaginary values

Ionic Electro-Optic Response: Raman and Mode Polarity

$$4\pi \sum_m \frac{1}{\omega_m^2} \left(\underbrace{\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha)}_{\text{Raman susceptibility tensor}} \right) \times \left(\underbrace{\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta)}_{\text{Mode polarity}} \right)$$



- The lowest frequency mode shows the strongest Raman response.
- Combined with the mode polarity, mode 4 contributes to Pockels tensor significantly.

Ionic Pockels tensor for Cm BaTiO₃

$$4\pi \sum_m \frac{1}{\omega_m^2} \left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right) \times \left(\sum_{\kappa', \beta} Z_{\kappa', \gamma\beta}^* u_m(\kappa'\beta) \right)$$

[111]	[$\bar{1}\bar{1}$]	[$\bar{1}11$]	[$\bar{1}\bar{1}\bar{1}$]
$\begin{bmatrix} 1812 & -1583 & -25 \\ -1584 & 1812 & -25 \\ -11 & -11 & 41 \\ -767 & 824 & -6 \\ 817 & -760 & -6 \\ 22 & 52 & -12 \end{bmatrix}$	$\begin{bmatrix} 1811 & 1582 & -25 \\ -1583 & -1810 & -25 \\ -11 & 11 & 41 \\ 767 & 824 & 6 \\ 817 & 759 & -6 \\ -22 & 52 & 12 \end{bmatrix}$	$\begin{bmatrix} -1806 & -1578 & -25 \\ 1578 & 1806 & -25 \\ 11 & -11 & 41 \\ 765 & 822 & -6 \\ 815 & 757 & 6 \\ 22 & -52 & 12 \end{bmatrix}$	$\begin{bmatrix} -1810 & 1581 & -25 \\ 1582 & -1809 & -25 \\ 11 & 11 & 41 \\ -766 & 823 & 6 \\ 816 & -758 & 6 \\ -22 & -52 & -12 \end{bmatrix}$

Electronic Pockels Tensor (pm/V)

$$\begin{bmatrix} 0 & 0 & 0.7 \\ 0 & 0 & 0.7 \\ 0 & 0 & 2 \\ 0 & 0.76 & 0 \\ 0.76 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$$

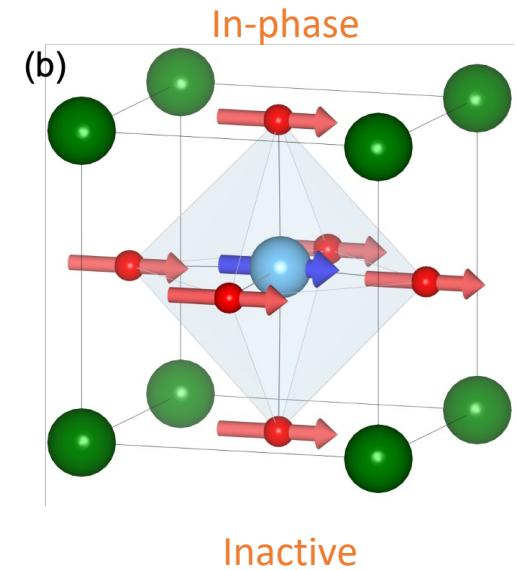
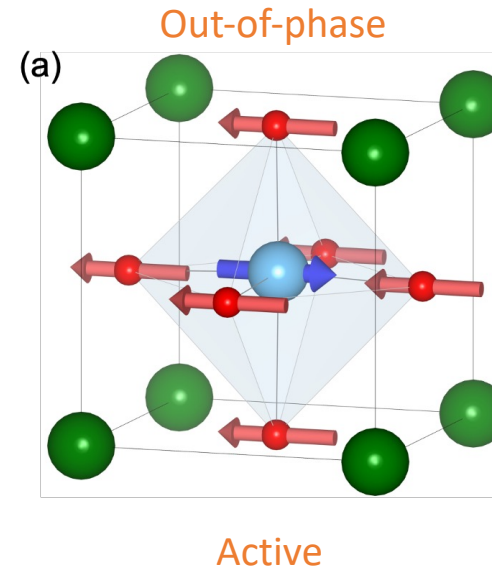
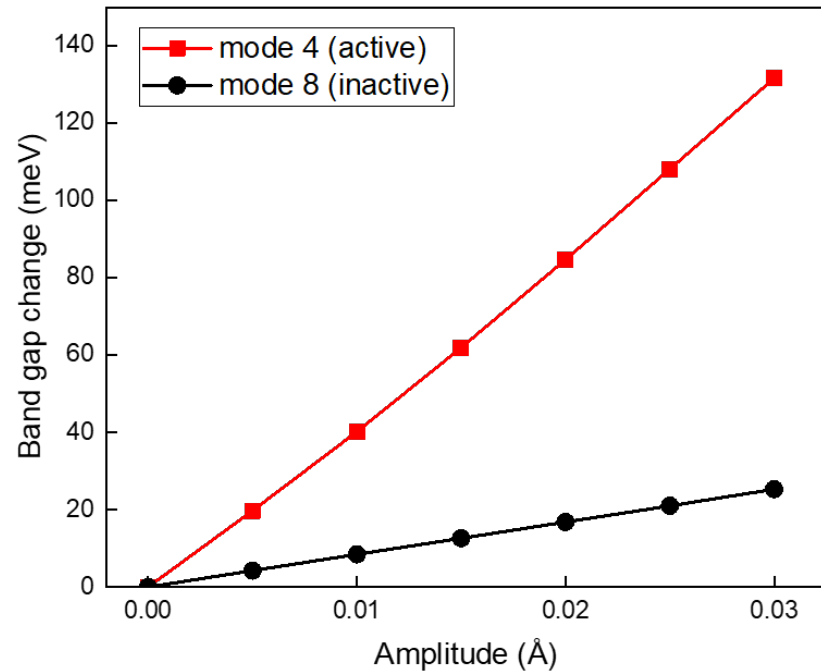
Ionic Pockels Tensor (pm/V)

$$\begin{bmatrix} 1.8 & 0.5 & -25 \\ -1.8 & 0.25 & -25 \\ 0 & 0 & 41 \\ 0.25 & 823 & 0 \\ 816 & 0.5 & 0 \\ 0 & 0 & 0 \end{bmatrix}$$

Exp. $r_{42}^{\text{clamped}} = 730$ pm/V

Difference between Raman active and inactive mode

$$\left(\sum_{\kappa, \alpha} \frac{\partial \chi_{ij}^{(1)}(\mathbf{R}, \eta_0)}{\partial \tau_{\kappa\alpha}} u_m(\kappa\alpha) \right)$$



- Active mode changes the orbital overlap and bond length significantly.
- Inactive mode shows the translation characteristic.

Piezo Electro-Optic tensor

$$r_{ij\gamma}^{\text{piezo}} = \underbrace{p_{ij\mu\nu}}_{\text{Piezoelectric tensor}} \underbrace{d_{\gamma\mu\nu}}_{\text{Elasto-optic tensor}}$$

$$p_{ij\mu\nu} \approx \frac{\Delta(\epsilon_{ij}^{-1})(\eta^+) - \Delta(\epsilon_{ij}^{-1})(\eta^-)}{2\eta_{\mu\nu}} + \mathcal{O}(\eta^2) \quad \text{Finite difference method}$$

Elasto-optic Element	<i>Cm</i>	<i>P4mm</i>	Expt. [67]
p_{11}	0.93	0.53	0.50
p_{12}	0.058	0.61	0.11
p_{13}	0.087	0.42	0.2
p_{31}	0.037	0.37	0.07
p_{33}	0.80	0.0085	0.77
p_{44}	0.81	0.17	1.0

Main contribution for r_{42}

	This work	Other Theory [68]	Expt.
d_{31} (pC/N)	40	15	33 [67], 34 [69]
d_{33} (pC/N)	38	90	90 [67], 85.6 [69]
d_{42} (pC/N)	469	10	282 [67], 392 [69]


Main contribution for r_{42}

Elasto-optic Element	<i>Cm</i>	<i>P4mm</i>	Expt. [67]
r_{13}^{piezo} (pm/V)	3.5	2	-2
r_{33}^{piezo} (pm/V)	30	6	65
r_{42}^{piezo} (pm/V)	760	81	570

Cm phase gives the better result

- *Cm* phase provides a better explanation of piezo EO tensor compared to *P4mm* phase

Nature of electro-optic response in tetragonal BaTiO₃

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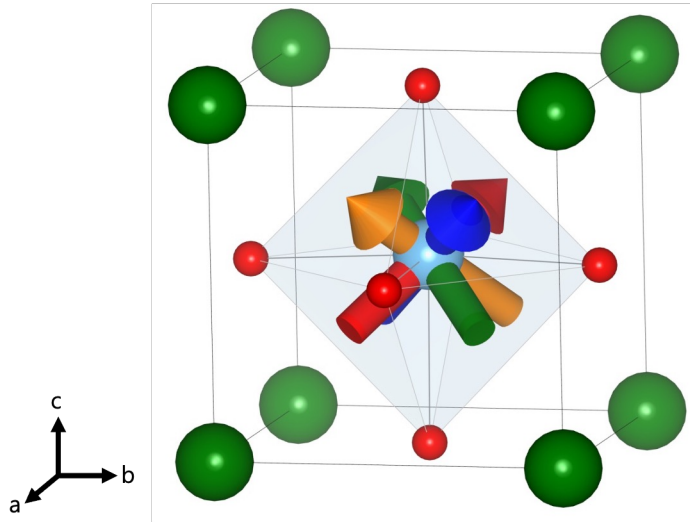
Barium titanate, BaTiO₃ (BTO), has emerged as a promising electro-optic material with applications in silicon photonics. It boasts one of the largest known electro-optic coefficients; however, the origin of this giant electro-optic response has not been investigated in detail and is poorly understood. Here we report on a first-principles study of the electro-optic or Pockels tensor in tetragonal $P4mm$ BTO. We find good agreement with experiment if the $P4mm$ structure is viewed as a dynamic average of four lower symmetry Cm structures. The large value of the Raman component of the EO coefficient is attributed to a low frequency and strong electron-phonon coupling of the lowest optical mode, and we trace the equally large piezoelectric contribution to the large components of the piezoelectric and elasto-optic tensors.

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Conclusions

$$r_{ij\gamma}^{elec} + r_{ij\gamma}^{ion} + r_{ij\gamma}^{piezo}$$

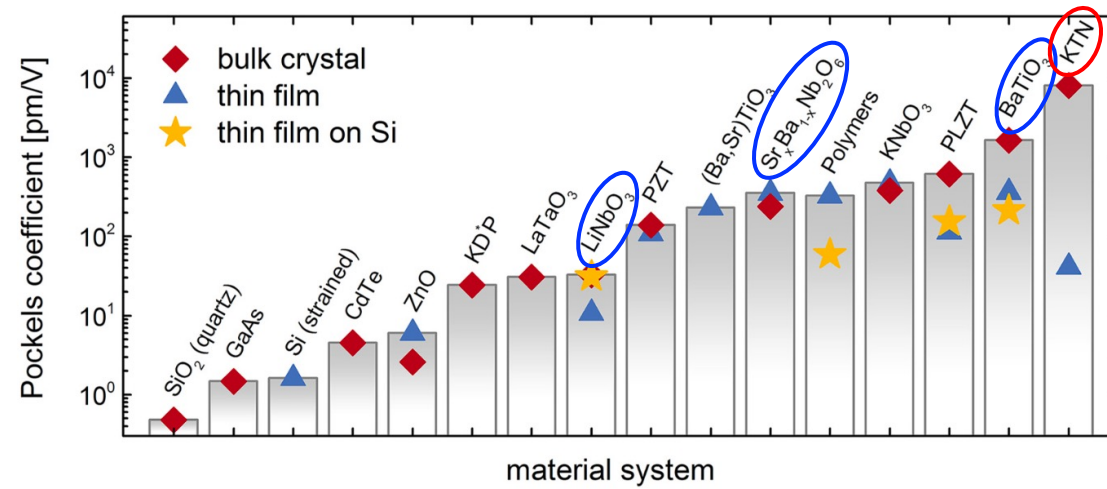
[111]-averaged tetragonal phase



Theory	Experiment
Unclamped Pockels tensor (p^m/v)	Unclamped Pockels tensor (p^m/v)
$\begin{bmatrix} 0 & 0 & 21.5 \\ 0 & 0 & 21.5 \\ 0 & 0 & 70 \\ 0 & 1560 & 0 \\ 1560 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$	$\begin{bmatrix} 0 & 0 & 8 \\ 0 & 0 & 8 \\ 0 & 0 & 105 \\ 0 & 1290 & 0 \\ 1290 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$

- Piezoelectric electro-optic response contributes almost a half of the Pockels tensor
- Cm averaged tetragonal phase better explains the linear electro-optic response than $P4mm$
- Strong EO response comes from the combination of a low phonon frequency and Raman-active mode.

Future work



- Identifying microscopic origin in LiNbO₃
- Calculating Pockels response in KTa_{0.5}Nb_{0.5}O₃
- Calculating ionic and piezo Pockels response in VASP using finite difference
- Exploring the how the domain structure affect the Pockels response

Supplementary materials

The Linear Electro-Optic Response: the Pockels Effect

$$\Delta \left(\frac{1}{n^2} \right) = \Delta (\varepsilon^{-1})_{ij} = \sum_{\gamma} r_{ij\gamma} E_{\gamma}$$

$r_{ij\gamma}$: Pockels coefficient (tensor) or electro-optic tensor

$$\Delta (\varepsilon^{-1})_{ij} = -\varepsilon_{im}^{(-1)} \Delta \varepsilon_{mn} \varepsilon_{nj}^{(-1)}$$

$$\begin{aligned} & \left[\frac{d\varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{dE_{\gamma}} \right]_{\mathbf{R}_0, \eta_0, E=0} && R: \text{coordinate}, \eta: \text{strain}, E: \text{electric field} \\ = & \left[\frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{\partial E_{\gamma}} \right]_{E=0} + \underbrace{\left[\frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{\partial \tau_{\kappa\alpha}} \right]_{\mathbf{R}_0} \frac{\partial \tau_{\kappa\alpha}}{\partial E_{\gamma}}}_{\text{Ionic term}} + \underbrace{\left[\frac{\partial \varepsilon_{ij}(\mathbf{R}, \eta_0, E)}{\partial \eta_{\mu\nu}} \right]_{\eta_0} \frac{\partial \eta_{\mu\nu}}{\partial E_{\gamma}}}_{\text{Piezoelectric term}} \end{aligned}$$

Expand the full differential of the dielectric tensor into electronic, ionic, and piezoelectric contributions

Clamped Electro-Optic Response

Electronic Pockels tensor (pm/V)	Ionic Pockels tensor (pm/V)
$\begin{bmatrix} 0 & 0 & 0.7 \\ 0 & 0 & 0.7 \\ 0 & 0 & 2 \\ 0 & 0.76 & 0 \\ 0.76 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$	$\begin{bmatrix} 0 & 0 & -25 \\ 0 & 0 & -25 \\ 0 & 0 & 40 \\ 0 & 820 & 0 \\ 820 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$
Clamped Pockels tensor (exp.) (pm/V)	
$\begin{bmatrix} 0 & 0 & 10 \\ 0 & 0 & 10 \\ 0 & 0 & 40 \\ 0 & 720 & 0 \\ 720 & 0 & 0 \\ 0 & 0 & 0 \end{bmatrix}$	

- Cm phase provides a better explanation of piezo EO tensor compared to $P4mm$ phase

Elasto-Optic Tensor Test Calculations

$$\underline{r_{ij\gamma}^{piezo}} = p_{ij\mu\nu} d_{\gamma\mu\nu} \quad p_{ij\mu\nu} \approx \frac{\Delta(\varepsilon_{ij}^{-1})(\eta^+) - \Delta(\varepsilon_{ij}^{-1})(\eta^-)}{2\eta_{\mu\nu}} + \mathcal{O}(\eta^2)$$

	LDA	PBE	PBEsol	LDA (QE)	Other theory references	Experiment
Si						
p_{11}	-0.0914	-0.105	-0.0971	-0.101	-0.098, -0.111	-0.094
p_{12}	0.0124	0.0121	0.0152	0.010	0.007, 0.020	0.017
Diamond						
p_{11}	-0.261	-0.268	-0.262	-0.263	-0.264	-0.248
p_{12}	0.0734	0.0471	0.0717	0.061	0.076	0.044
NaCl						
p_{11}	0.0727	0.101	0.0943	0.058	0.077	0.155
p_{12}	0.16	0.163	0.171	0.153	0.157	0.161
MgO						
p_{11}	-0.3	-0.292	-0.2859	-0.299	-0.310, -0.218	-0.259
p_{12}	-0.42	-0.0545	-0.04627	-0.042	-0.050, 0.013	-0.011

- Finite difference to calculate the elasto-optic tensor (Voigt notation)
- The test calculation describes the elasto-optic tensor fairly well compared to corresponding experiment value